

Angle-resolved photoemission spectroscopy (ARPES): applications to quantum materials

QS3 Summer School

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UC Davis

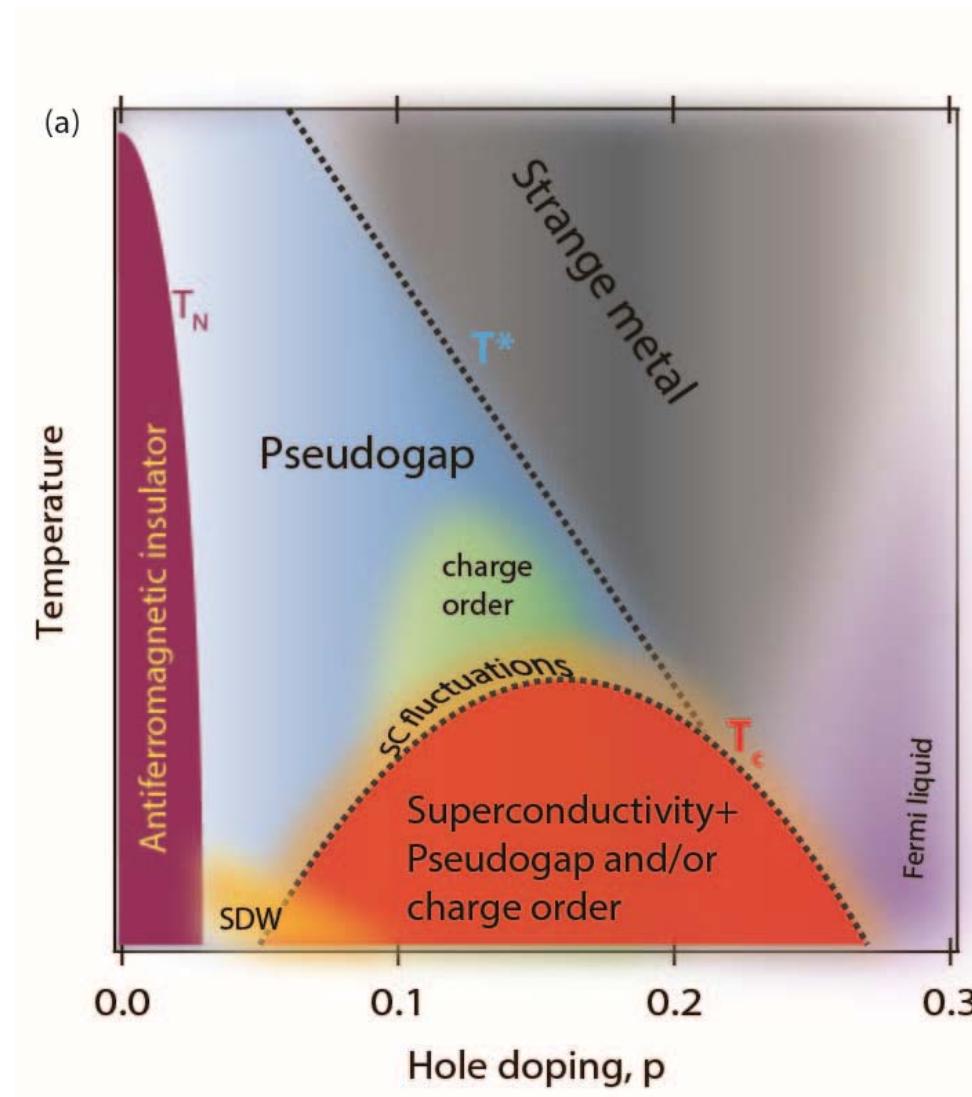


Theme

Emergent phenomena in quantum materials are readily characterized by photoemission, and problems in quantum materials drive development of experimental technology

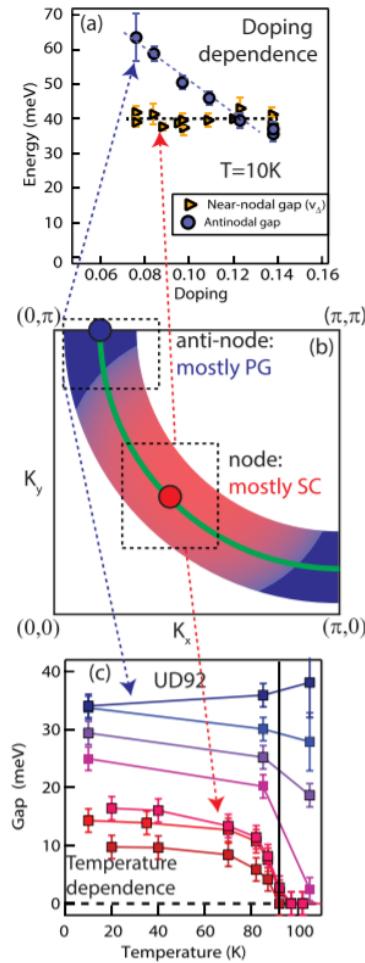
- Cuprates
- Iron-based superconductors
- Topological insulators
- Dirac materials
- 2D materials

Complex phase diagram in cuprates

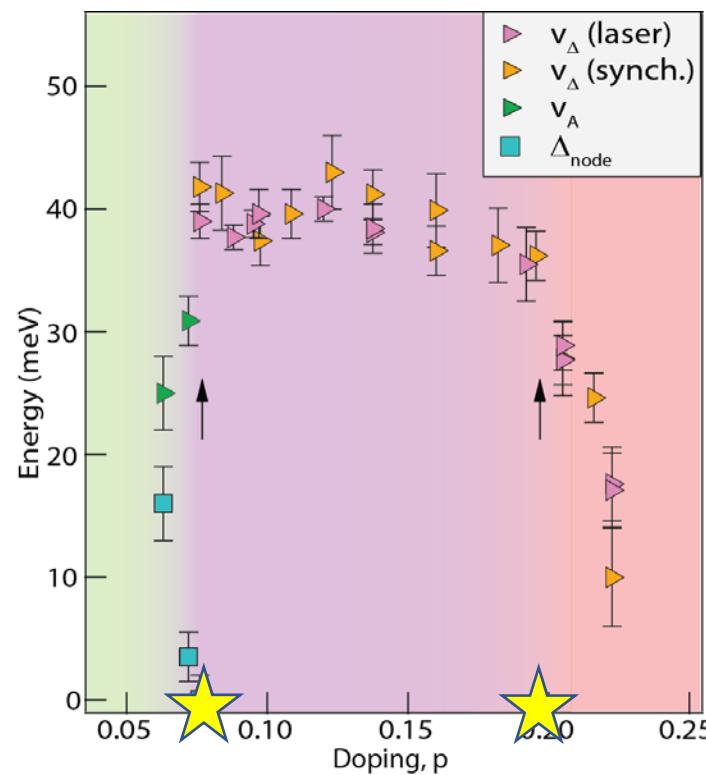


Progress towards understanding phase diagram via gap measurements

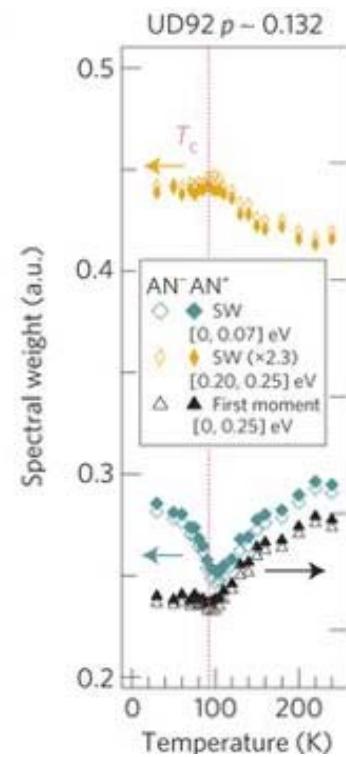
Pseudogap and superconductivity are distinct phases



Phase boundaries of pseudogap and SDW phase inside superconducting dome

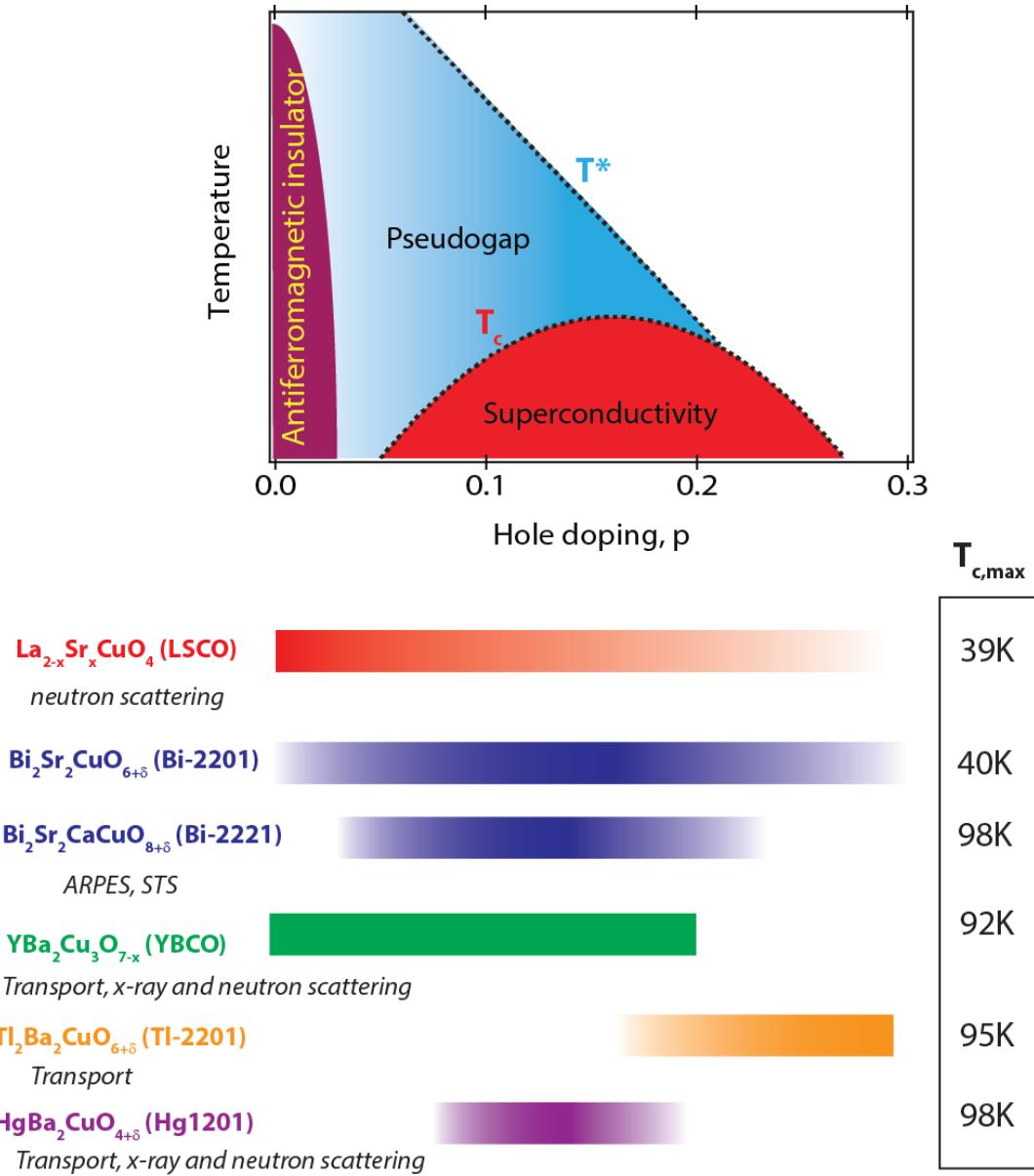


Competition between superconductivity and pseudogap



- W. S. Lee, I. Vishik, *et al* Nature **450** (2007)
- I. Vishik *et al* PNAS **109** (2012)
- M. Hashimoto *et al* Nat. Phys. **14** (2015)

Remaining questions



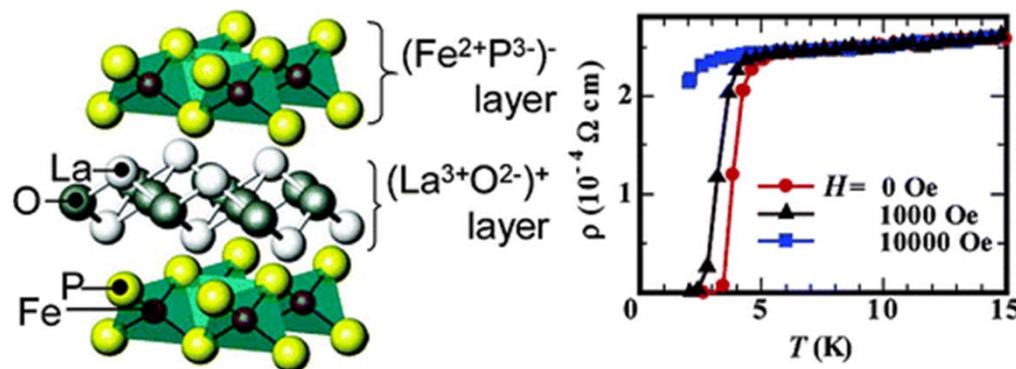
- Mechanism of SC and PG
- Universal vs materials dependent properties
- Is the overdoped side really conventional?
- Many obvious experiments that were never repeated
 - Isotope effect
 - Heat capacity through T^*

Iron-based high temperature superconductors

A multiband system for a momentum-resolved probe

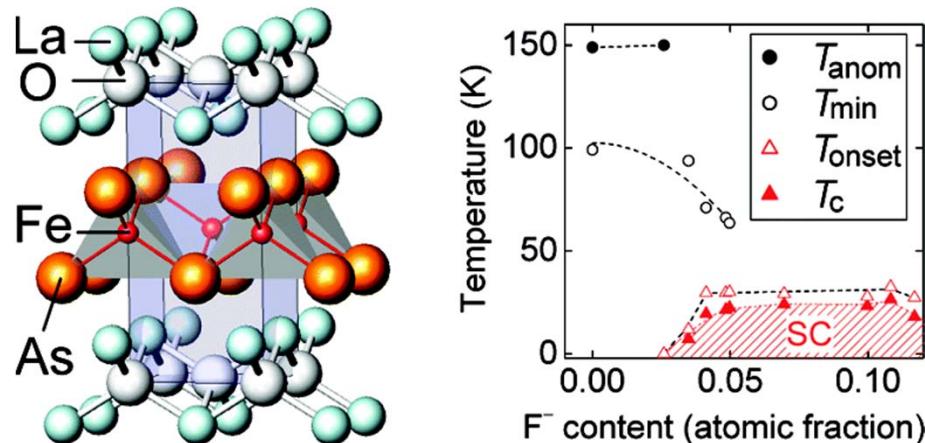
Discovery of Fe-based SCs

2006: LaFePO, T_c=5K



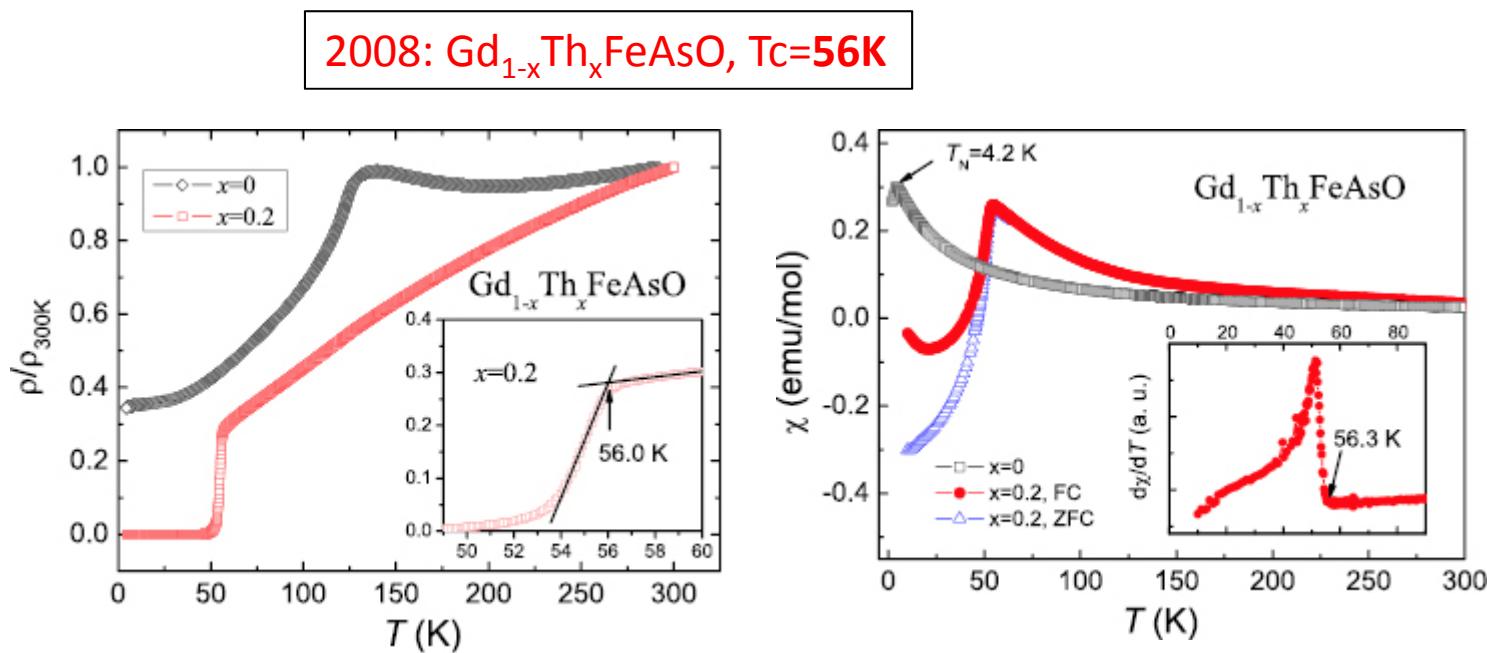
Kamihara et al, *J. Am. Chem. Soc.*, **128**, pp 10012–10013 (2006)

2008: LaFeP[O_{1-x}F_x], T_c=26K



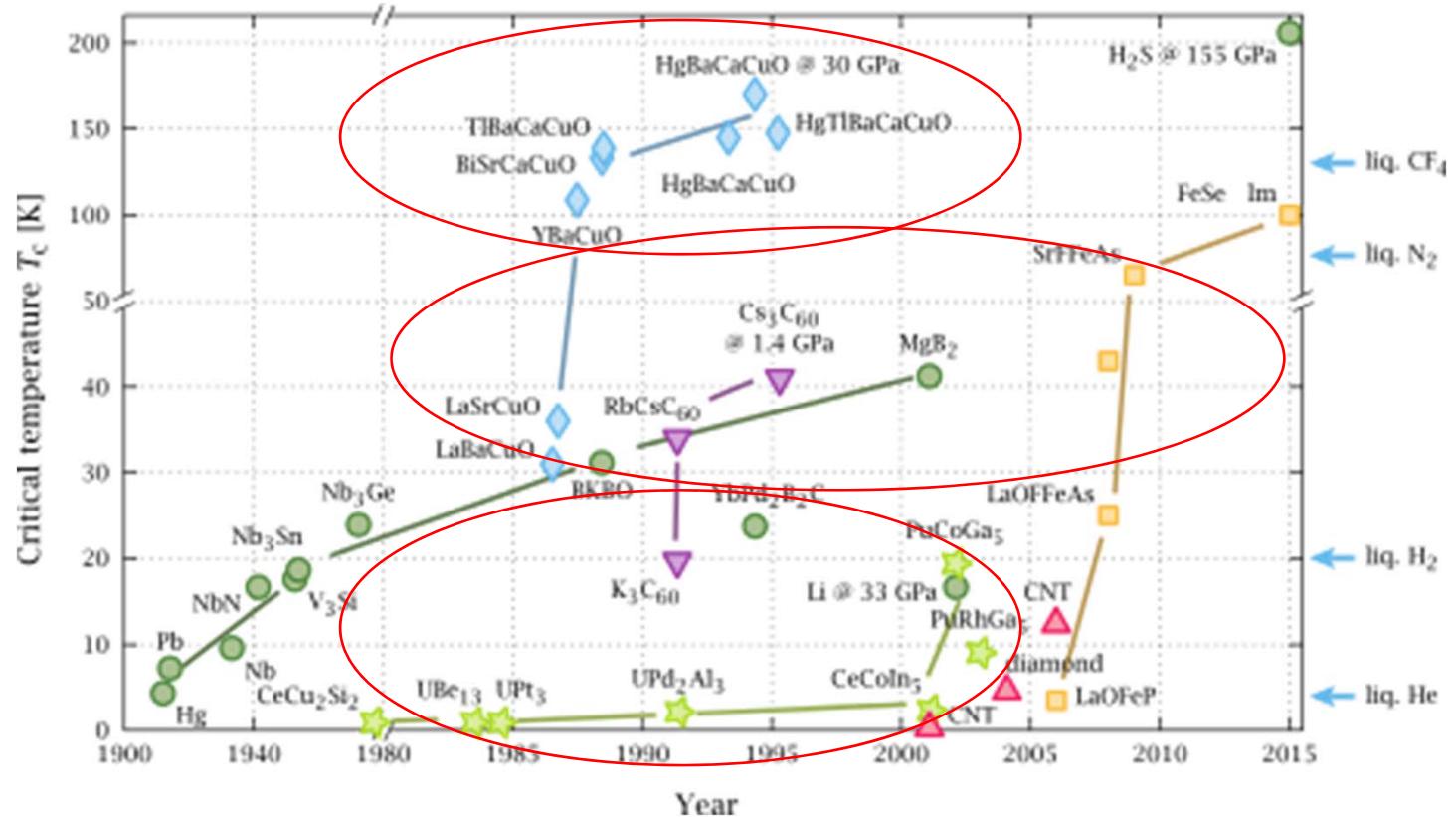
Kamihara et al., *Am. Chem. Soc.*, **130**, pp 3296–3297 (2008)

Discovery of Fe-based SCs



Wang *et al.* Europhys. Lett. **83** 67006 (2008)

What is high T_c ?

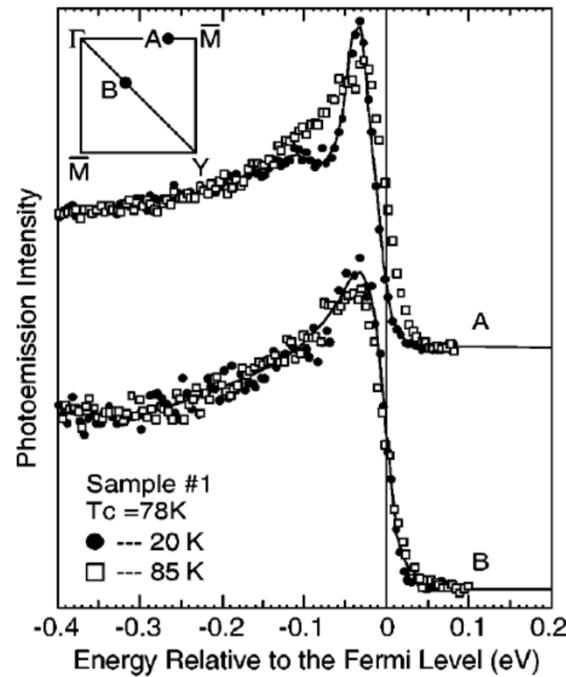


- $T_c > 77\text{K}$ (boiling point of liquid nitrogen)
- $T_c > 30\text{K}$ (former BCS “limit”)
- T_c large relative to Fermi energy
- Mechanism unknown (not BCS)

Image source:
https://en.wikipedia.org/wiki/High-temperature_superconductivity

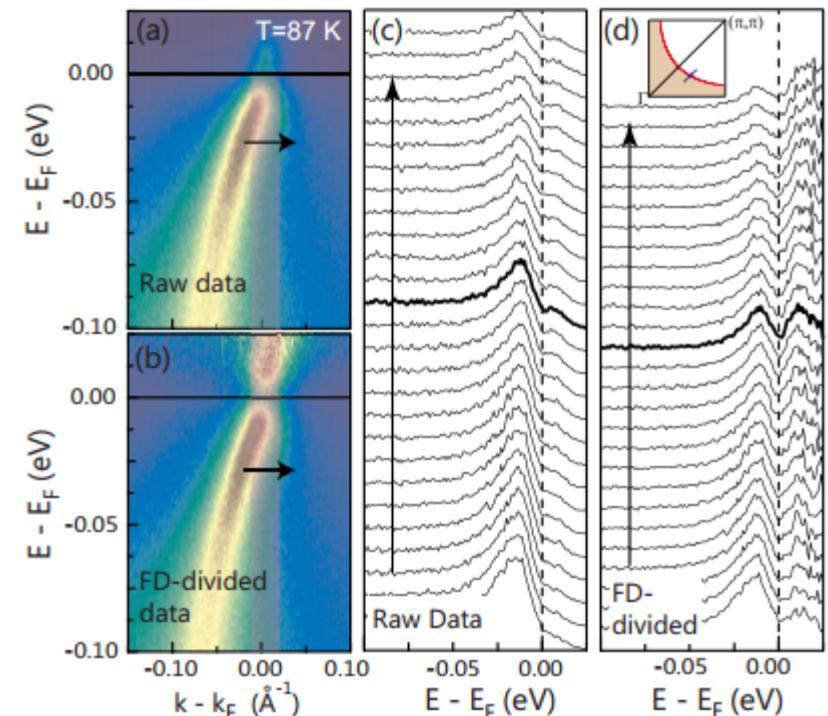
A second family of high- T_c materials!!

- High- T_c is not unique to one material class
- Benefit of hindsight
- Better tools



Shen *et al.* PRL **70** (1993)

- 1993:
- 6hrs per trace
 - One momentum at a time



Balatsky, Lee, Shen, PRB **79** (2009)

~2008

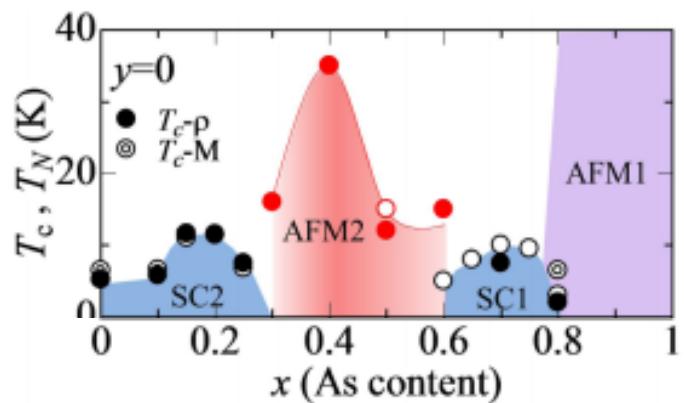
- ~10 mins per cut
- Many momenta at a time, along 1D trajectory in k -space

Questions when a new superconductor is discovered

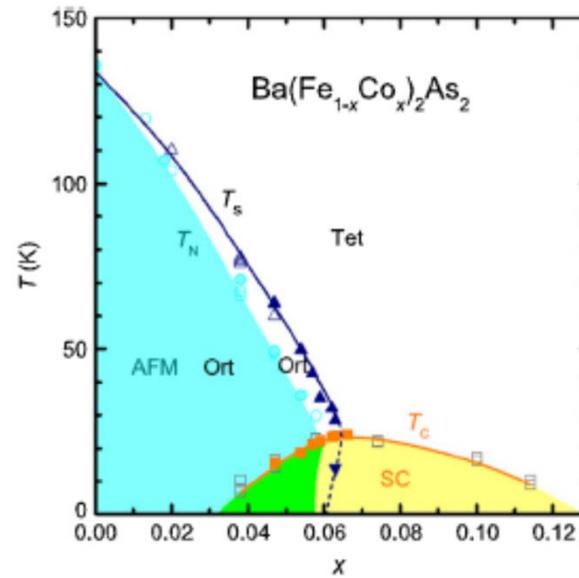
- What is its fermiology?
- What is its superconducting order parameter?
- What are nearby electronic phases?
- What is its mechanism?

(A small selection of) Fe-SC phase diagrams

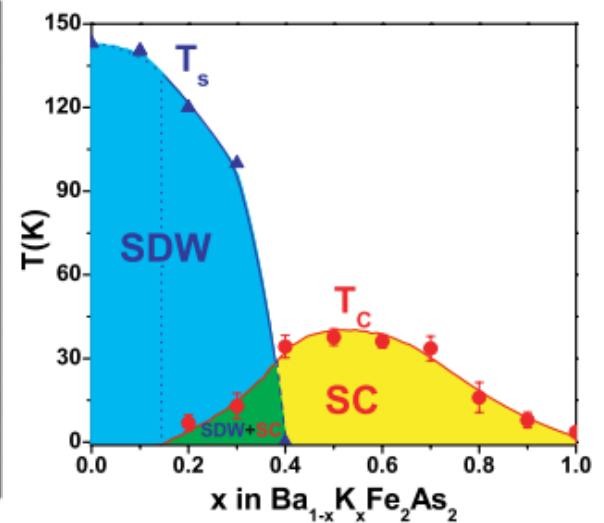
$\text{LaFe}(\text{P},\text{As})\text{O}$



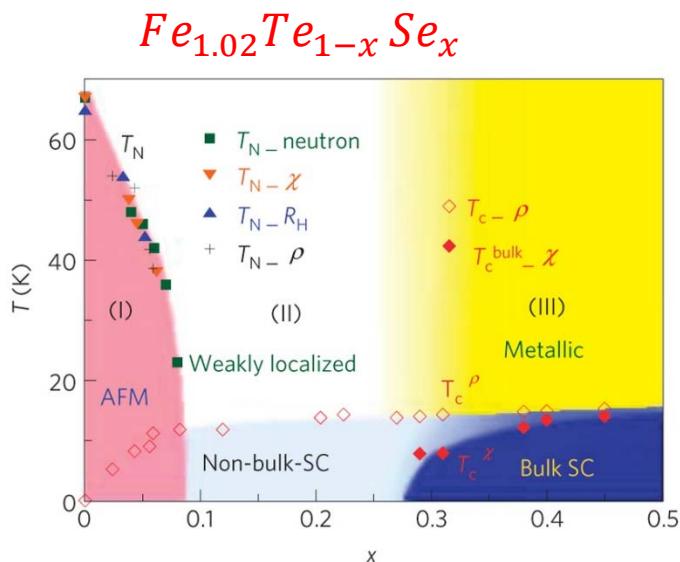
Lai *et al.*, PRB **90**, 064504 (2014)



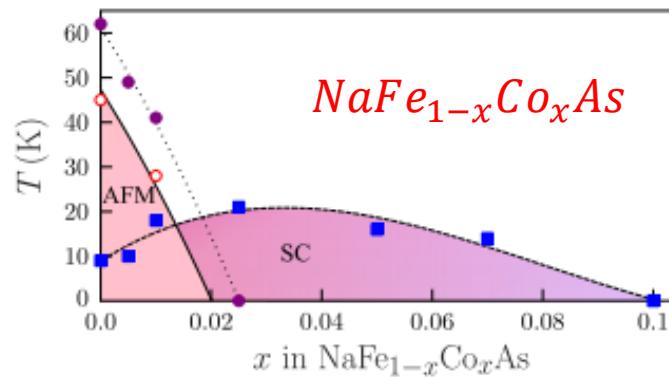
Nandi *et al.*, PRL **104**, 057006 (2010)



Chen *et al.*, EPL **85** 17006 (2009)

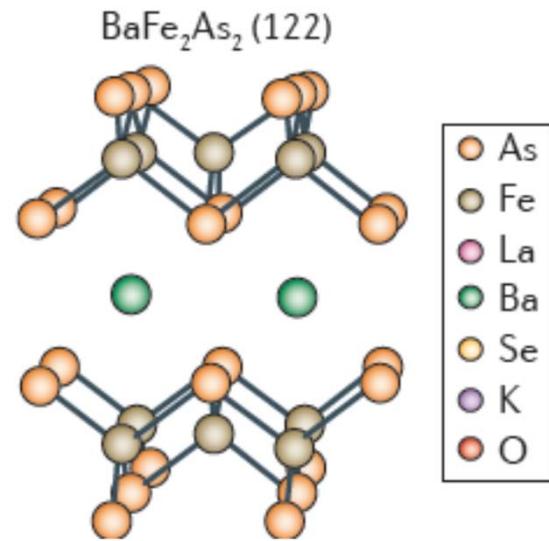


Liu *et al.*, Nat. Mater. **9**, 718–720 (2010)

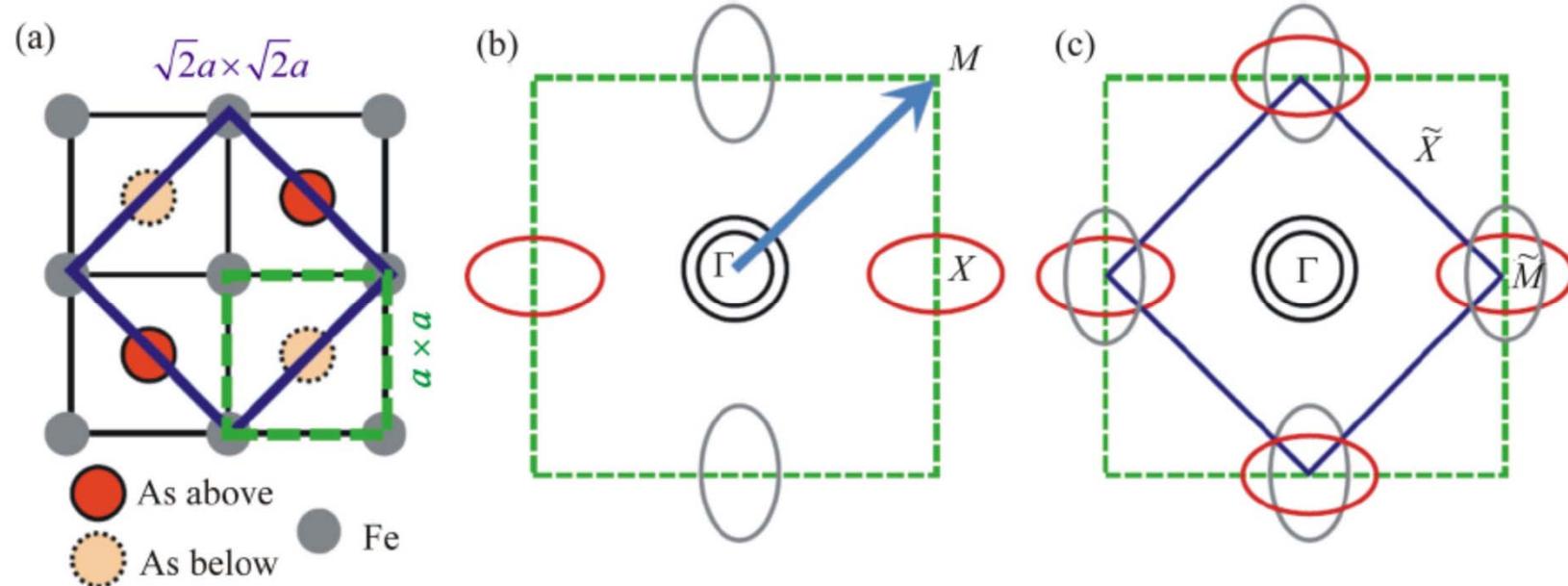


Parker *et al.*, PRL **104**, 057007 (2010)

Fe-SC Brillouin zone



- 1-Fe unit cell (ignore As/Se)
- 2-Fe unit cell (consider larger unit cell due to Fe/Se)
- Multiple Fermi surfaces: momentum-resolved tool is very useful!

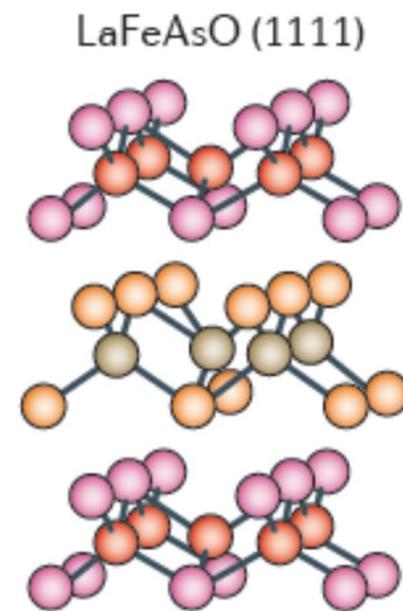
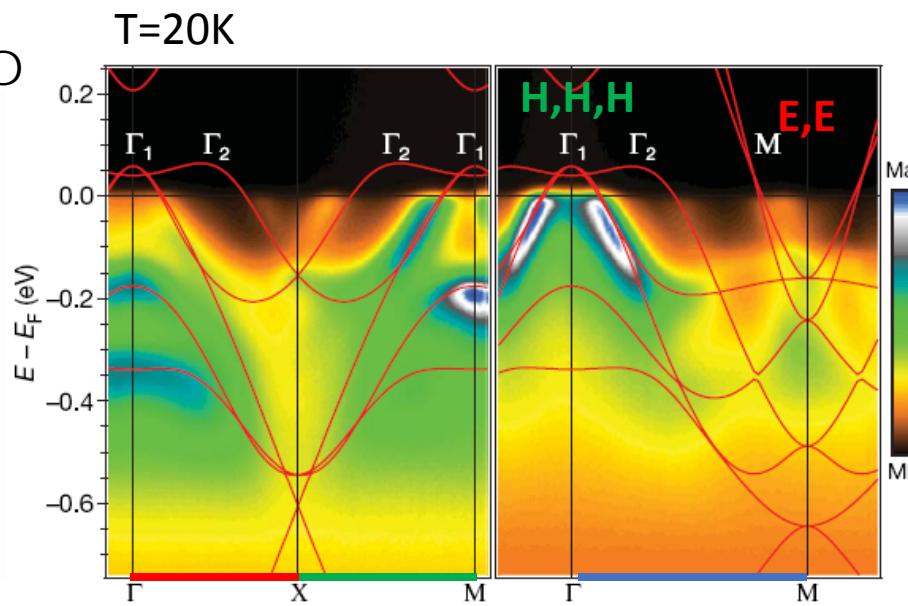
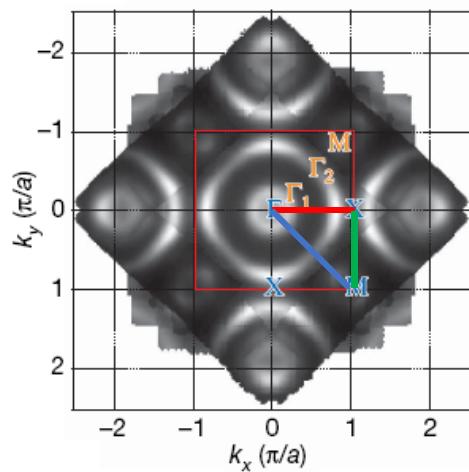


Kordyuk, *Low Temp Phys*, **38**, 888 (2012)

1111-Fermi surface

LaOFeP

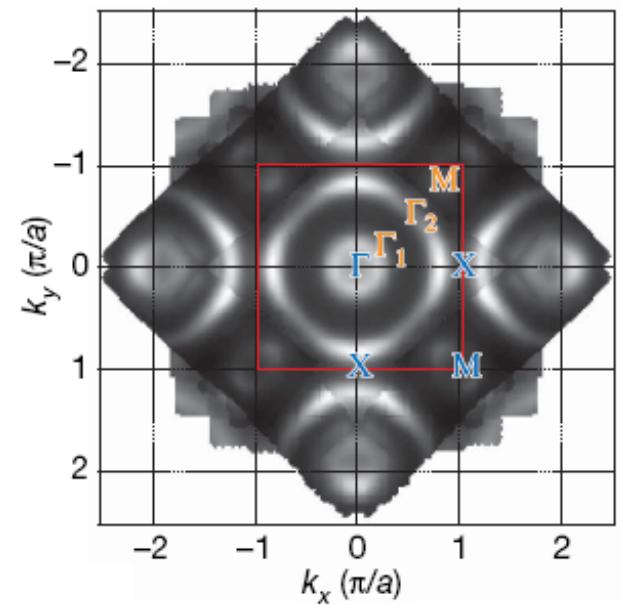
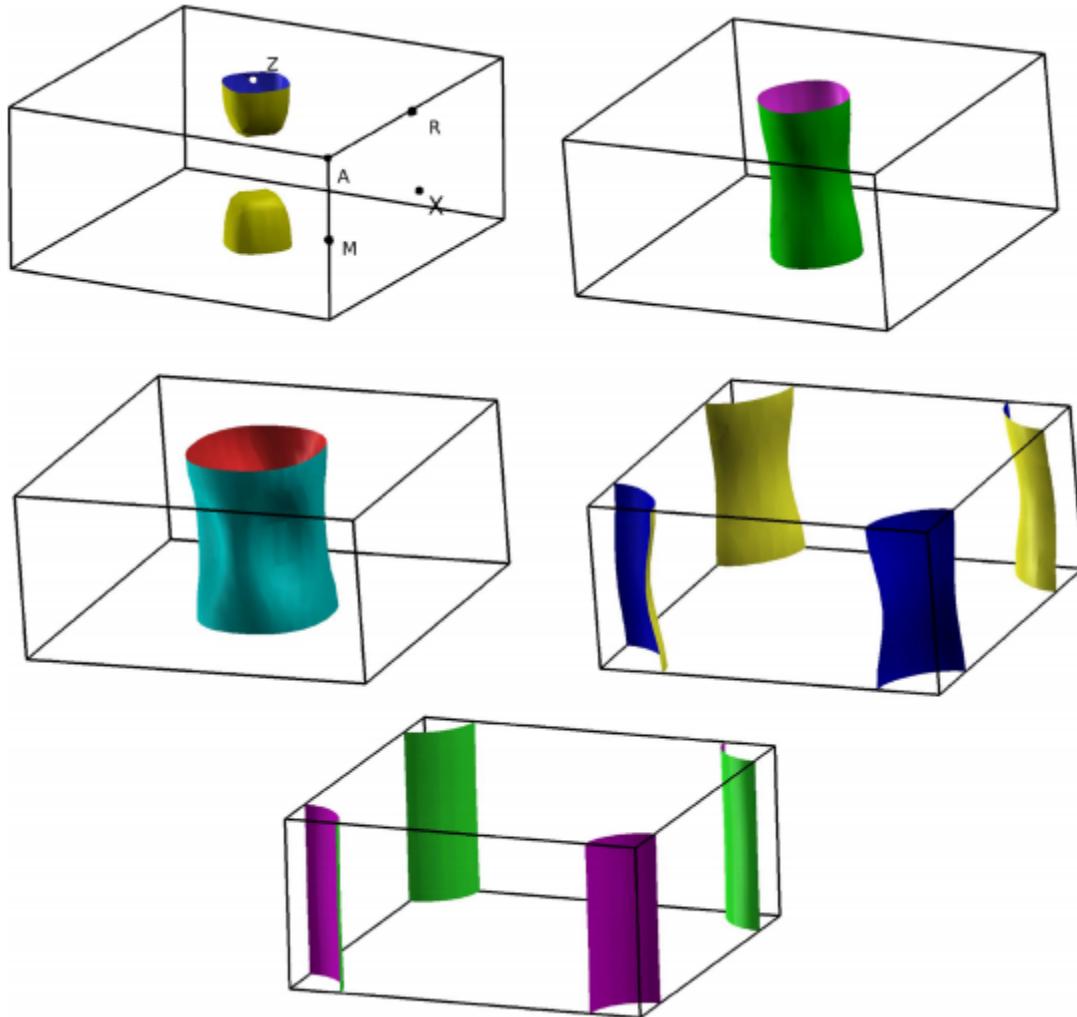
Now called: LaFePO



D. H. Lu, et al. Nature **455** 81
(2008)

“A quantitative agreement can be found between the angle-resolved photoemission spectra and the **calculated band dispersions** after **shifting the calculated bands up by 0.11 eV and then renormalizing by a factor of 2.2**.”

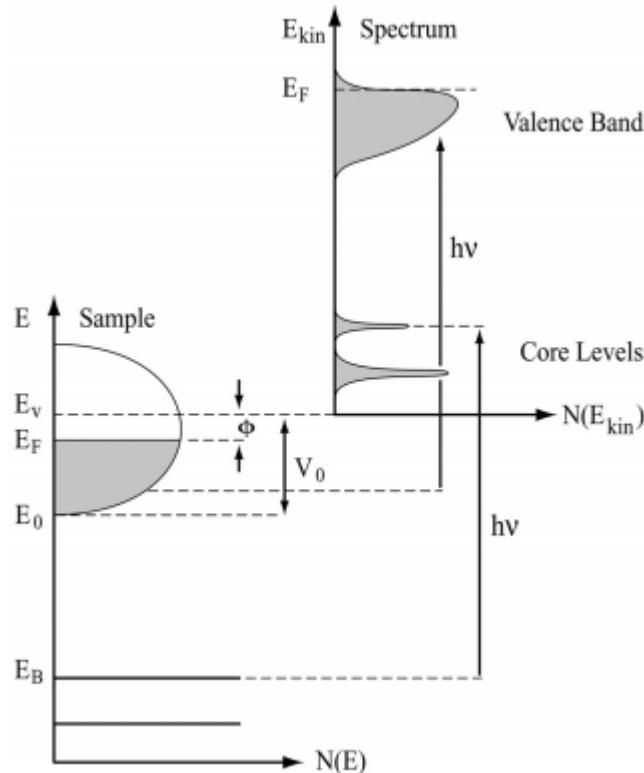
Comparison to Fermi surface calculations



S. Lebègue, PRB **75**, 035110 (2007)

k_z (k_{\perp}) in ARPES

Final state dispersion assumed to be free-electron-like: $E_f(\mathbf{k}) = \frac{\hbar^2 k^2}{2m} - |E_0| = \frac{\hbar^2(k_{\parallel}^2 + k_{\perp}^2)}{2m} - |E_0|$



$$E_{kin} = E_f - \Phi \quad \hbar k_{\parallel} = \sqrt{2mE_{kin}} \sin\vartheta$$

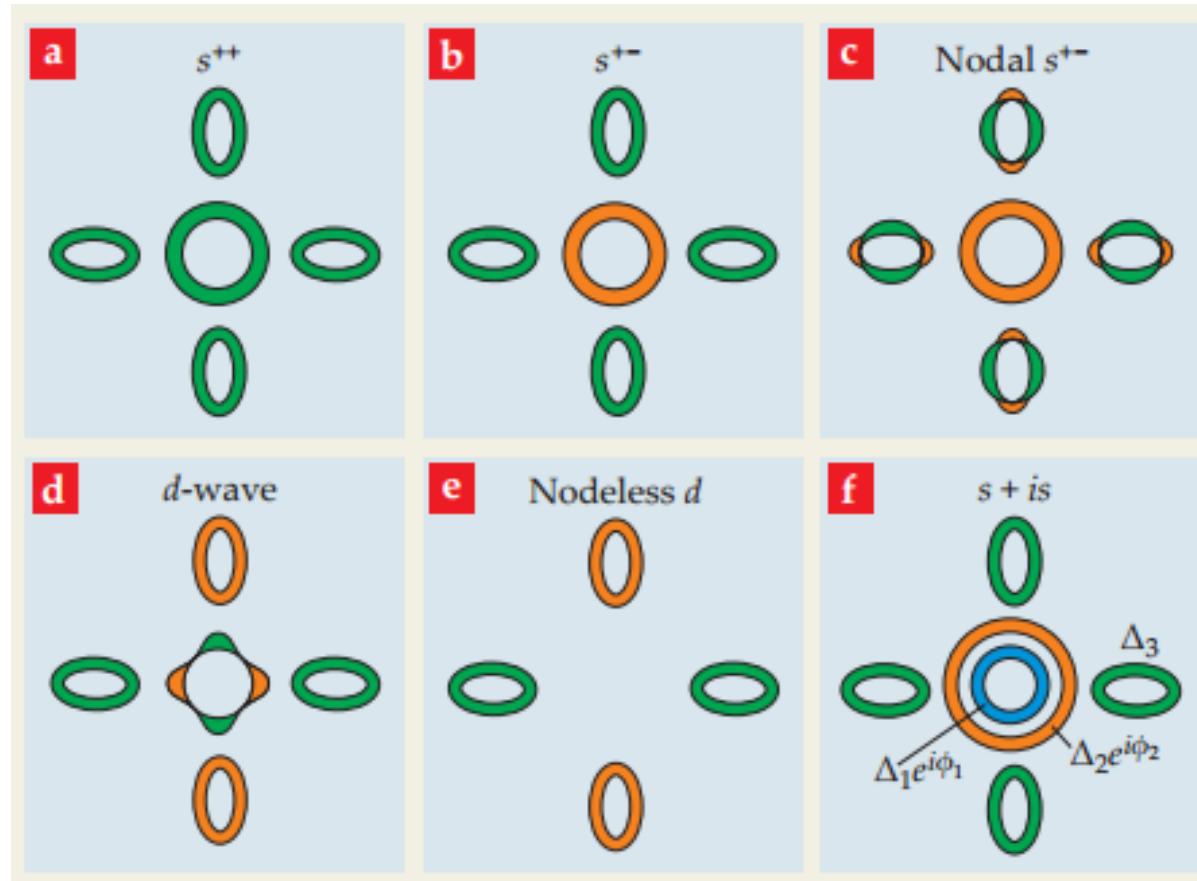
$$k_{\perp} = \frac{1}{\hbar} \sqrt{2m(E_{kin} \cos^2 \vartheta + V_0)}$$

V_0 =inner potential

Determined by:

- Comparison to band structure calculations
- Experimentally observed periodicity of $E_f(\mathbf{k})$, measured by varying photon energy
- Guess

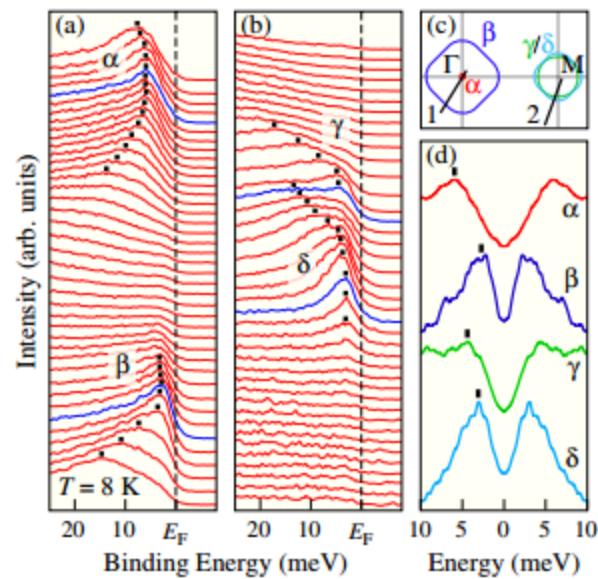
Potential gap symmetries



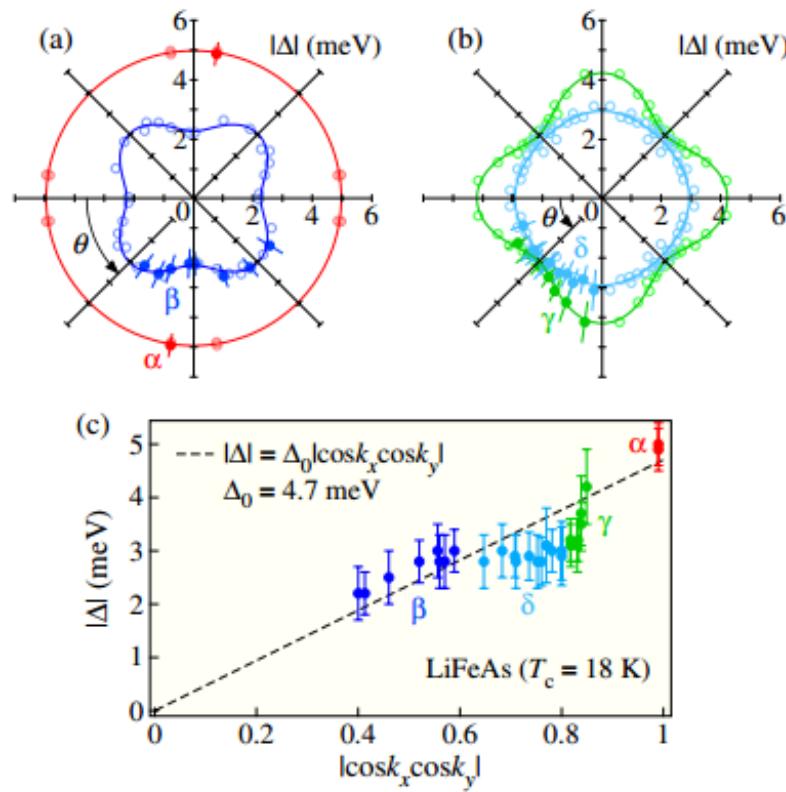
Chubukov and Hirschfeld, Phys. Today **68**, 46 (2015)

Results from ARPES: inconclusive

Superconducting gap in LiFeAs ($T_c=18\text{K}$)

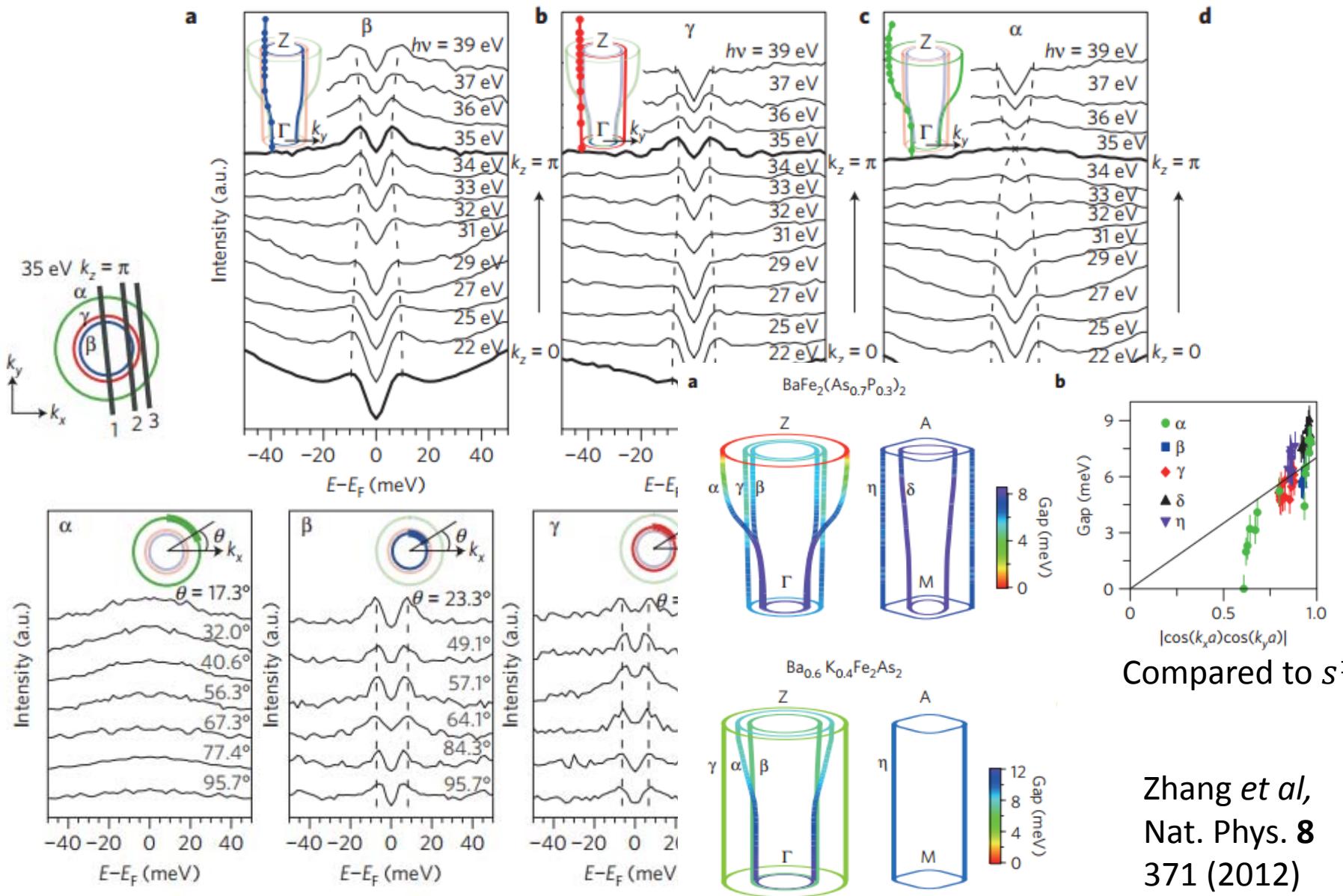


K. Umezawa *et al*, PRL
108, 037002 (2012)

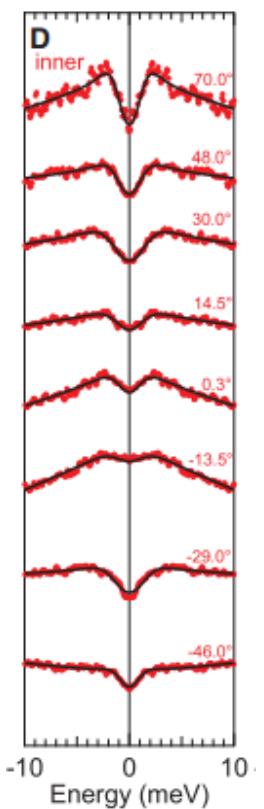
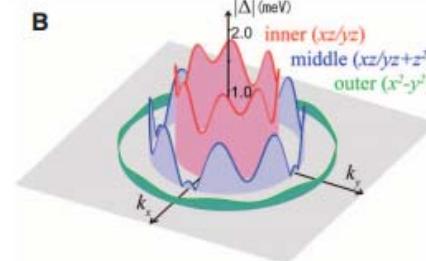
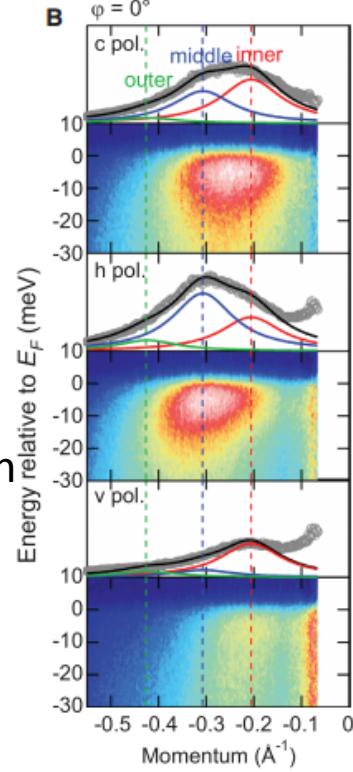
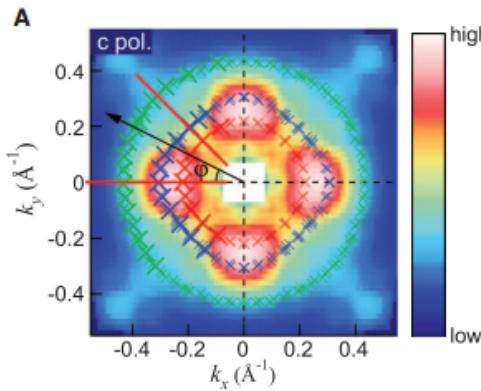


- Gaps are anisotropic but there are no nodes
- Consistent with s_{\pm} pairing

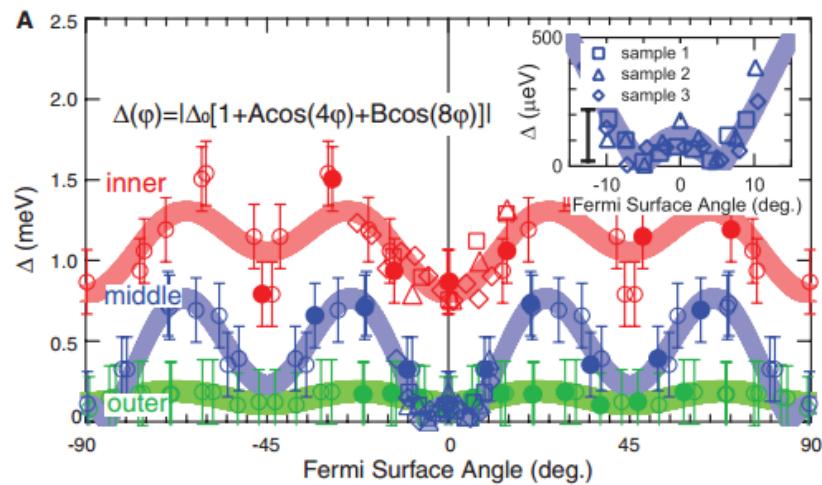
SC gap in $\text{BaFe}_2(\text{As}_{0.7}\text{P}_{0.3})_2$ ($T_c=30\text{K}$)



SC gap in KFe₂As₂ ($T_c=3.4K$)

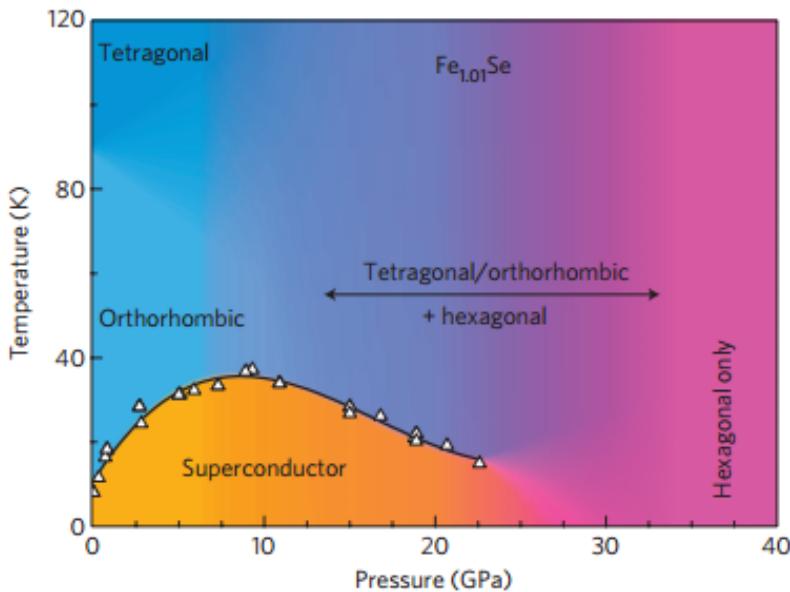


“An eight noded monster”



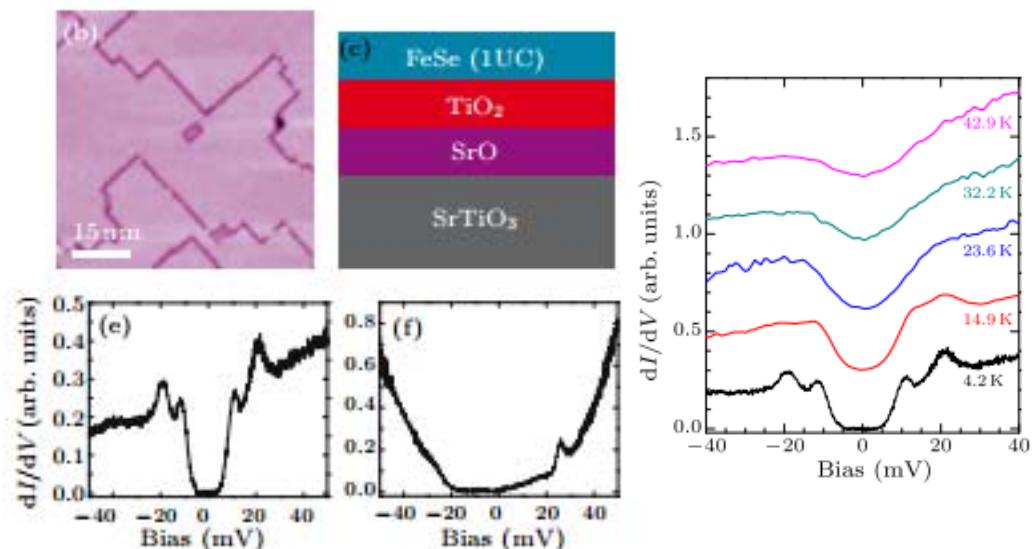
Okazaki *et al*, Science
337 p1314 (2012)

Monolayer FeSe



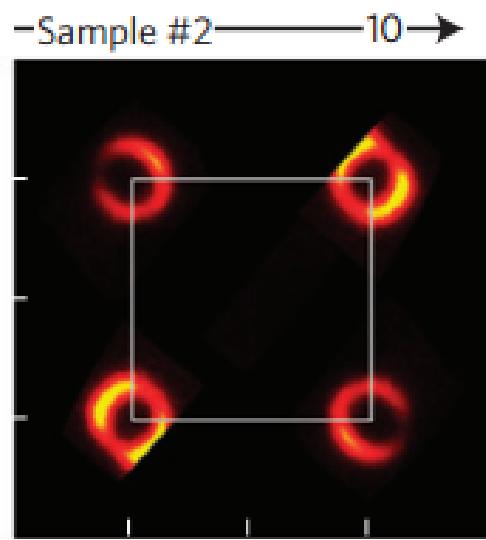
Bulk FeSe

- $T_c = 9\text{K}$ at ambient pressure
- T_c can be increased to 37K with pressure

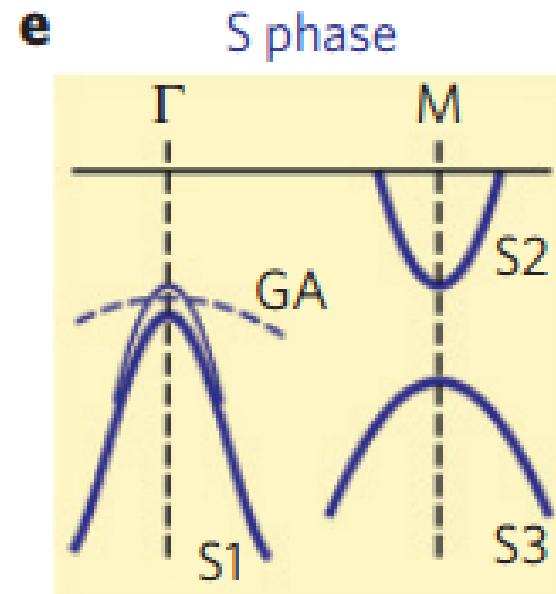


- Monolayer (1 unit cell) FeSe on SrTiO_3 (TiO_2 terminated)**
- Gap $\sim 20 \text{ meV} \rightarrow$ suggests high T_c
 - Gap persists to $> 50\text{K}$
 - Highest reported $T_c = 109\text{K}$, highest accepted $T_c = 65\text{K}$

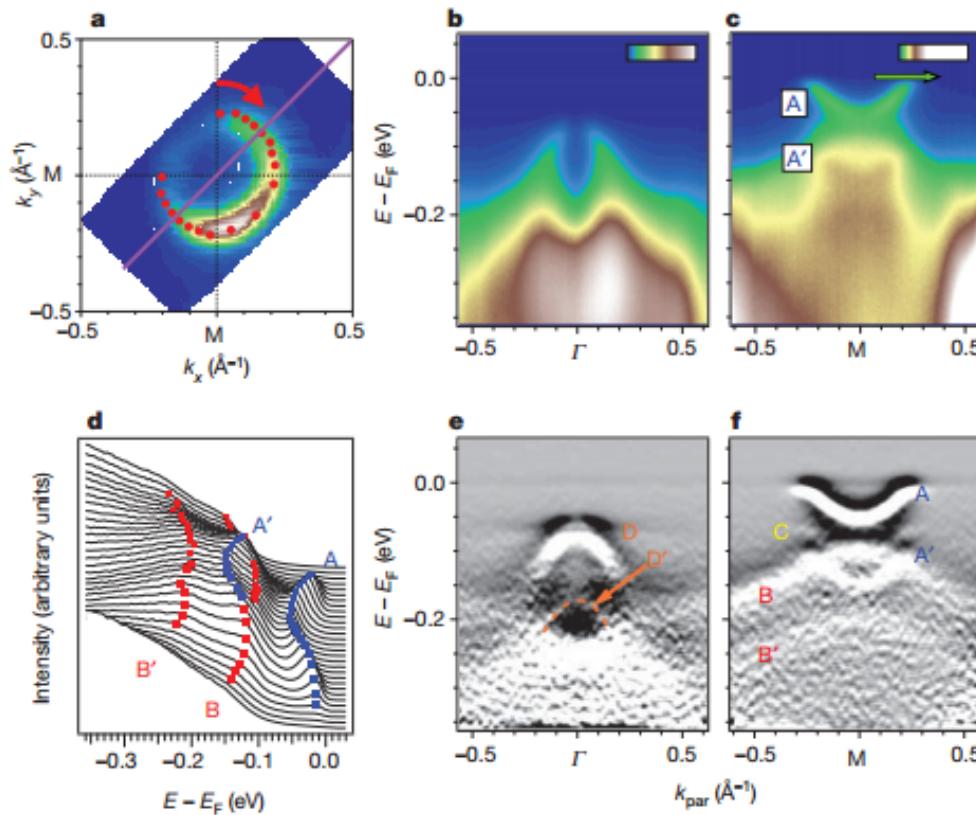
Monolayer FeSe: Fermiology



High-Tc FeSe monolayer does not have FS at Γ , unlike bulk FeSe and most other Fe-SCs



Monolayer FeSe: possible mechanism of T_c enhancement



- Observation: ‘copies’ of band structure in a way which is not consistent with quantum well state
- Interpretation: strong coupling to phonon mode in STO at $q=0$
- Consequence: interface e-ph coupling is responsible for T_c enhancement

Topological insulators

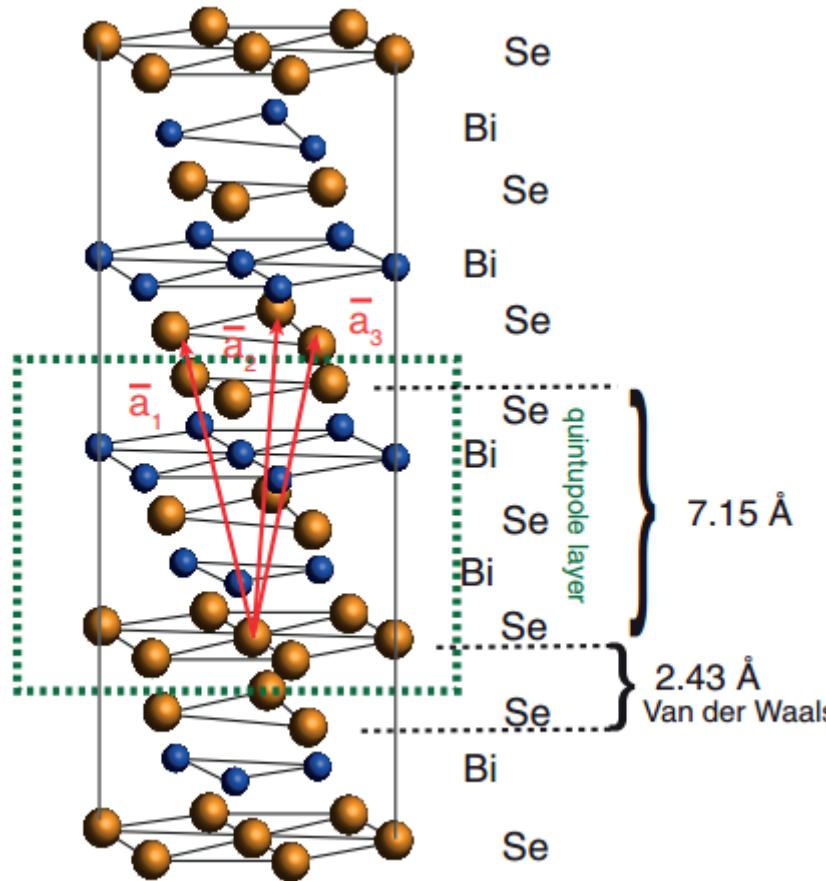
A standard candle for technique development

Expectations for ARPES spectra of 3D topological insulators

- Correlated electron systems and unconventional superconductors → Experiments drive theory
- Topological materials → Theory drives experiment
- Insulator in bulk
- Surface state
 - Odd number of them
 - Dirac-like dispersion
 - Spin-momentum locking
 - Difficult to destroy except by breaking time reversal symmetry

Topological insulator materials

- Bi_2Te_3
- Bi_2Se_3
- Sb_2Te_3
- $\text{Bi}_{2-x}\text{Sb}_x\text{Te}_{3-y}\text{Se}_y$



Bianchi *et al.* Semicond. Sci.
Technol. **27** 124001 (2012)

Materials history

PHYSICAL REVIEW

VOLUME 108, NUMBER 5

DECEMBER 1, 1957

Electrical and Thermal Properties of Bi_2Te_3

C. B. SATTERTHWAITE AND R. W. URE, JR.
Westinghouse Research Laboratories, Pittsburgh, Pennsylvania

(Received August 15, 1957)

Samples of both *n*-type and *p*-type Bi_2Te_3 containing from 3×10^{17} to 5×10^{19} extrinsic carriers were prepared and the phase diagram in the region about Bi_2Te_3 has been clarified. The Hall mobility parallel to the cleavage planes varies as $T^{-1.8}$ for holes and $T^{-2.7}$ for electrons. Room temperature values are $\mu_p = 420 \text{ cm}^2 \text{ v}^{-1} \text{ sec}^{-1}$ and $\mu_n = 270 \text{ cm}^2 \text{ v}^{-1} \text{ sec}^{-1}$. The energy gap is $E_g = 0.20$ electron volts. From thermal conductivity measurements over the temperature range from 77°K to 380°K the lattice conductivity was found to be $\kappa_L = 5.10 \times 10^{-2}/T$ watt-deg $^{-1}$ cm $^{-1}$. The sharp rise in the thermal conductivity in the vicinity of room temperature was attributed to transport of energy by ambipolar diffusion of electrons and holes.

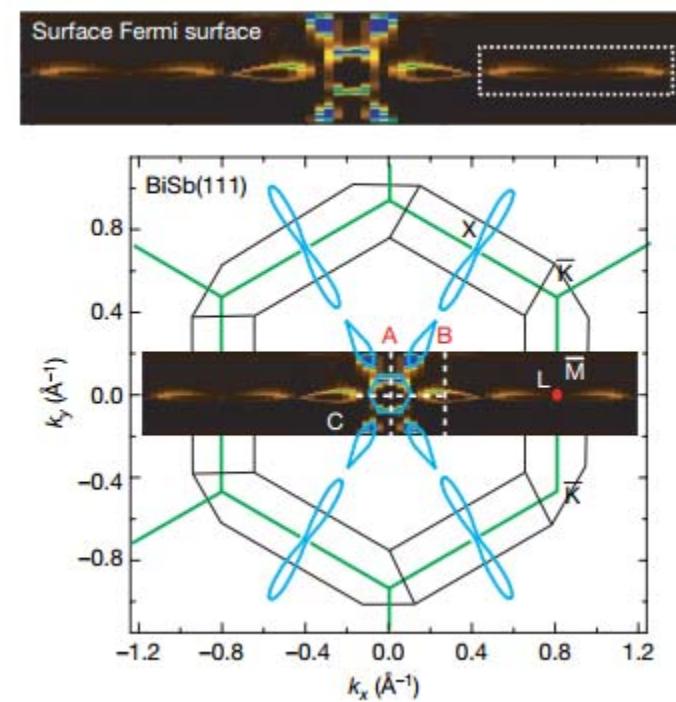
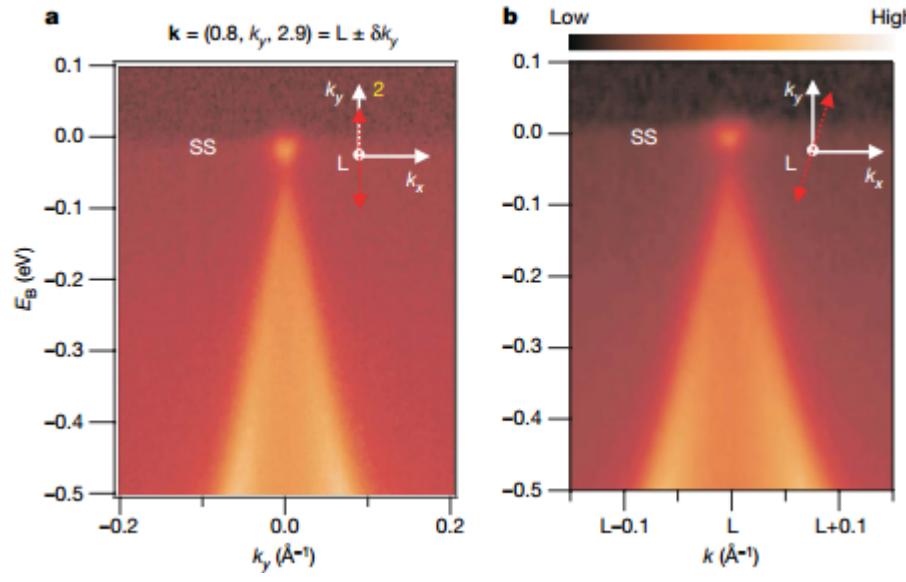
I. INTRODUCTION

BISMUTH telluride recently has been of considerable interest, particularly as a thermoelectric material; however, the electrical and thermal properties of this material have not been established. The present paper describes the preparation of bismuth telluride of known composition and a study of the thermal conductivity and the electrical properties of both *n*- and *p*-type material.

This was found not to be the case. Whether the starting material contained an excess of Bi or an excess of Te the zone refined Bi_2Te_3 contained approximately 2×10^{19} excess holes.

By the technique described below the details of the phase diagram in the region of Bi_2Te_3 were clarified and also a series of single crystal samples of varying carrier concentration were produced for studies of the electrical and thermal properties.

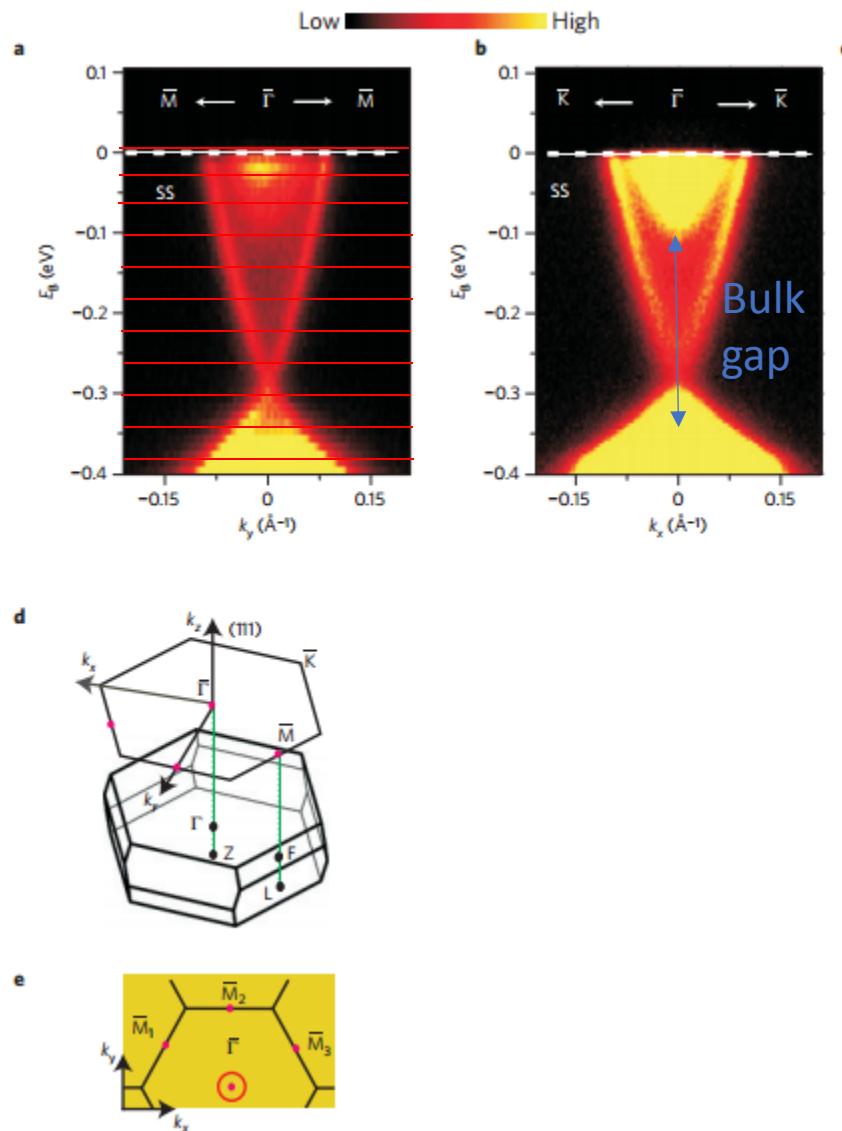
0th 3D Topological insulator: Bi_{1-x}Sb_x



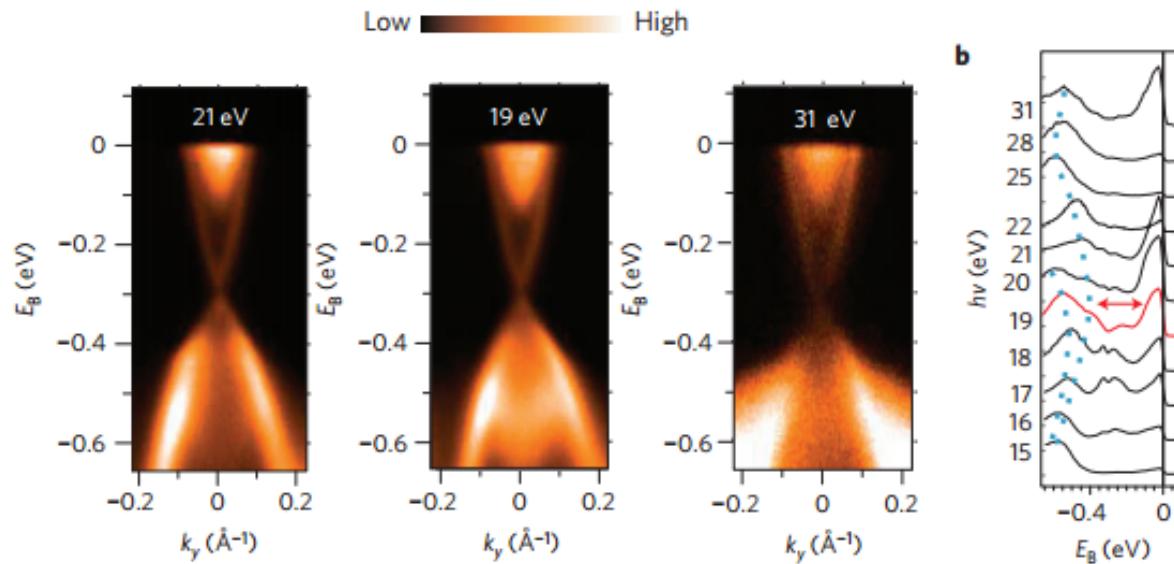
Problem: too many surface states

Hsieh *et al.* Nature 452 (2008)

1st 3D Topological insulator: Bi₂Se₃



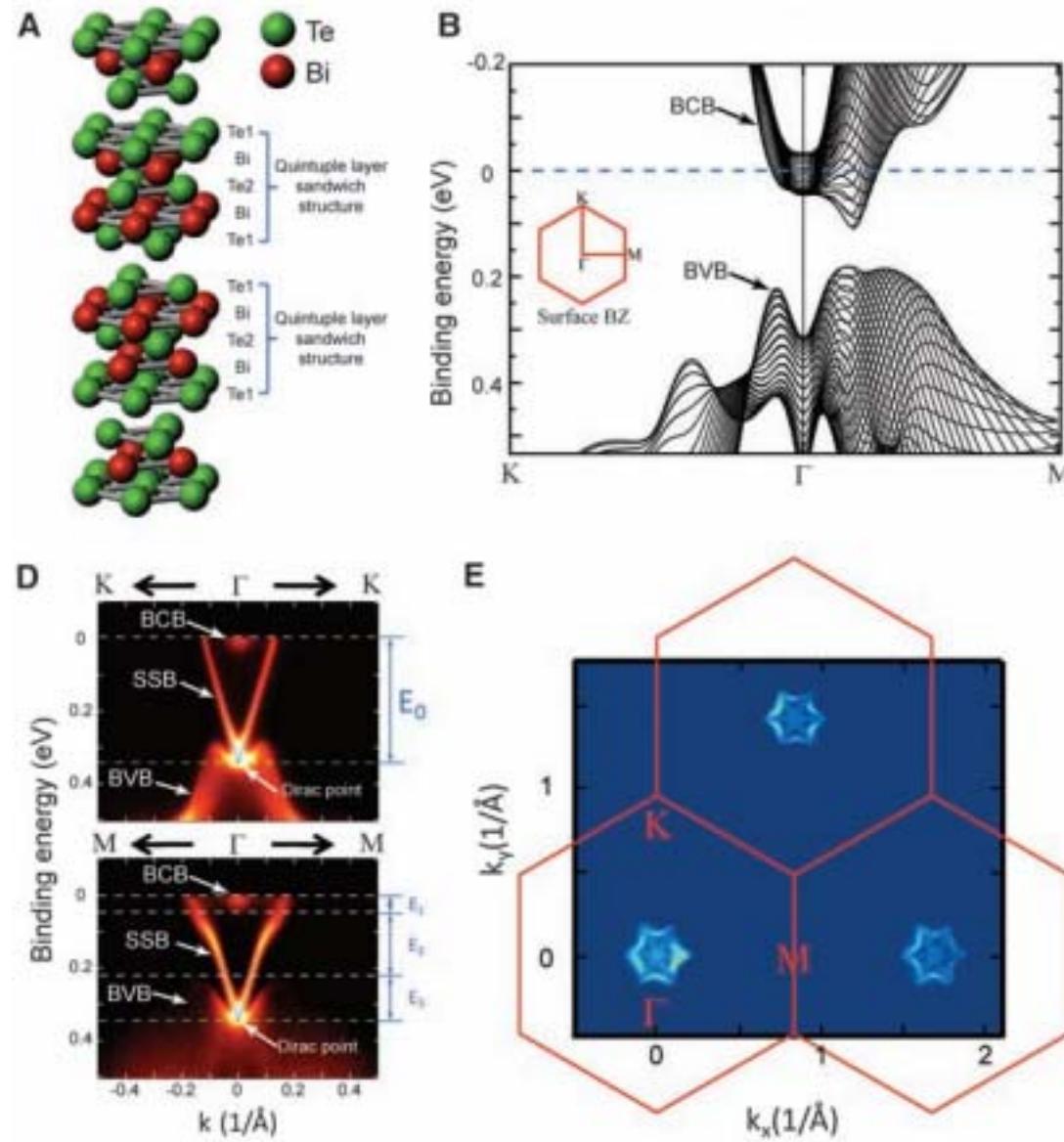
Distinguishing surface from bulk states



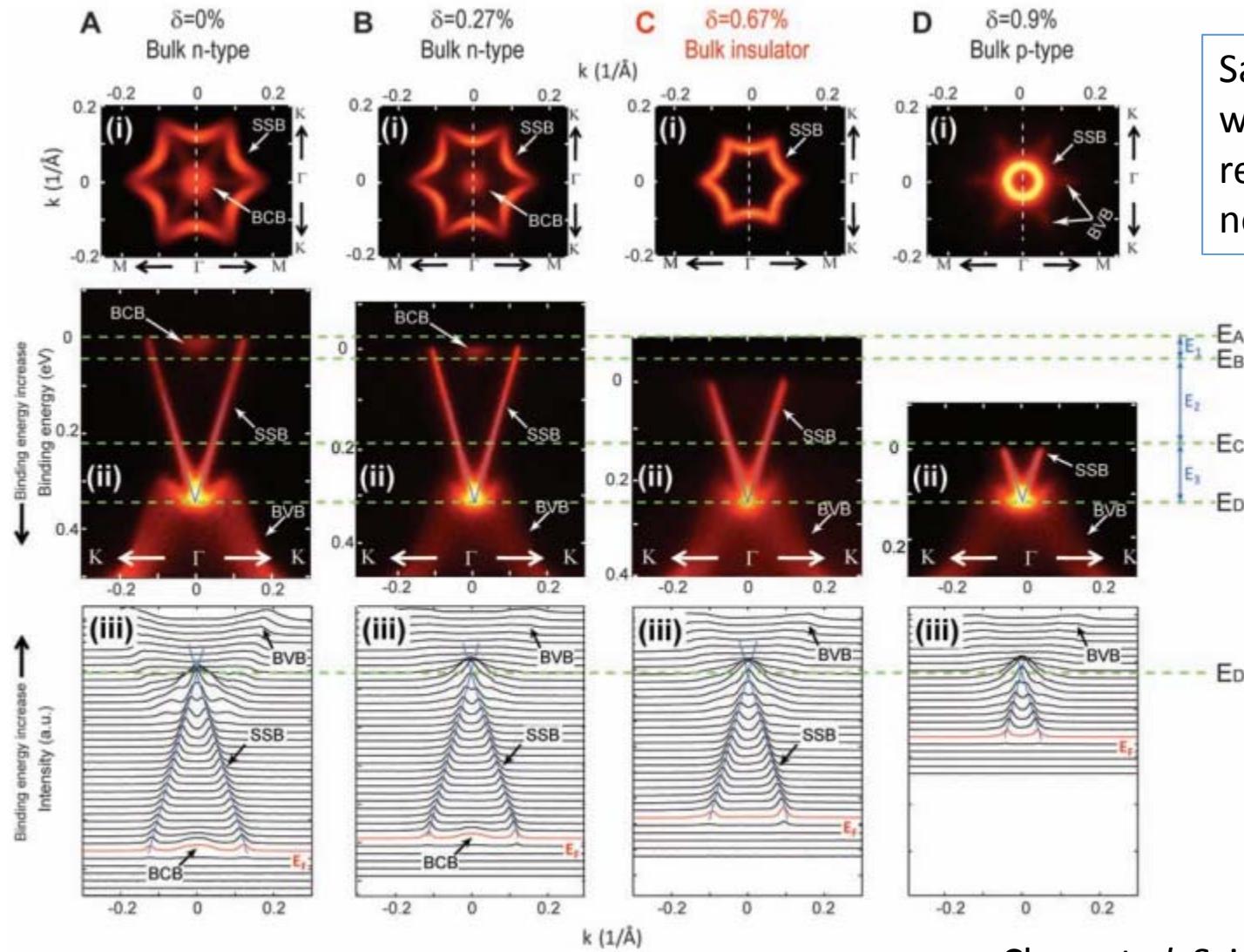
Vary photon energy

- Surface bands **do not** disperse because they are strictly 2D
- Bulk bands **do** disperse because they have some 3D character
- Complication: matrix element effects can make surface state look brighter or dimmer at different photon energies

2nd 3D topological insulator: Bi₂Te₃



Tuning doping: $(\text{Bi}_{1-\delta}\text{Sn}_\delta)_2\text{Te}_3$



Chen *et al.* Science 325 July 2009

Measuring spin texture via spin-resolved ARPES

Which of these is a really **bad** way of distinguishing different spin states via ARPES

- A. Mott scattering
- B. Stern Gerlach experiment
- C. Exchange scattering
- D. Circularly polarized light
- E. Ask a theorist

Spin texture via spin ARPES

How can we measure electron spin in photoemission experiments?

Method	Interaction	Operation voltage	S_{eff}	Figure of merit	Target
Mott	Spin-orbit	20–100 kV	0.1–0.2	$1\text{--}5 \times 10^{-4}$	Au thin film
SPLEED	Spin-orbit	150 V	0.2–0.3	$1\text{--}2 \times 10^{-4}$	W single crystal
Diffuse scattering	Spin-orbit	150 V	~0.2	$\sim 1 \times 10^{-4}$	Au thin film
VLEED	Spin-exchange	6–10 V	0.3–0.4	$\sim 10^{-2}$	Fe single crystal

1. Jozwiak *et al.* Rev. Sci. Instr. 81 (2010) 053904
2. Okuda *et al.*, Journal of electron spectroscopy and related phenomena 201 23 (2015)

Table source: A. Takayama, *High-resolution spin-resolved photoemission spectrometer and the Rashba effect in Bismuth thin films* (2015)

Mott Detectors

- Spin-orbit coupling (SOC): positively charged nucleus provides effective **B**-field in rest frame of electron:

$$\mathbf{B} = -\frac{1}{c} \boxed{\mathbf{v}} \times \mathbf{E} = -\frac{1}{c} \frac{Ze}{r^3} \mathbf{v} \times \mathbf{r} = \frac{Ze}{mc r^3} \mathbf{L}$$

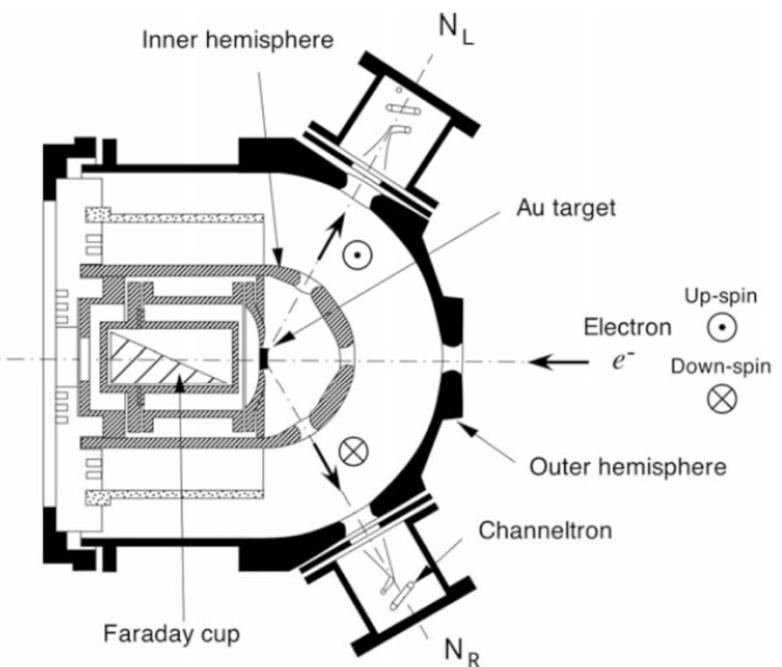
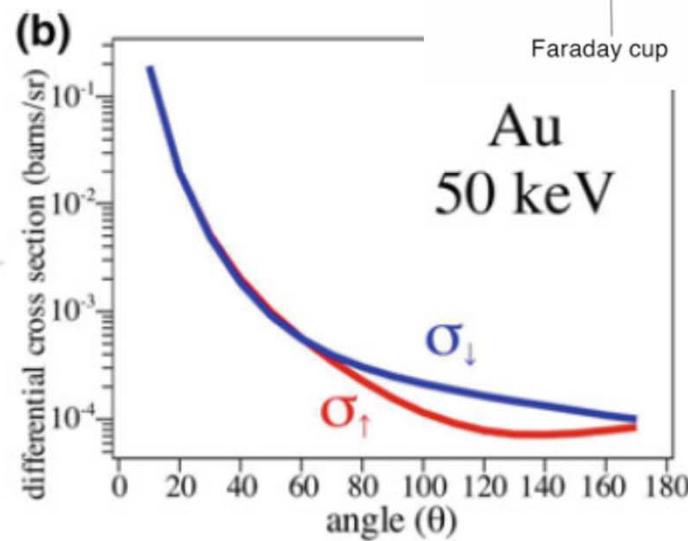
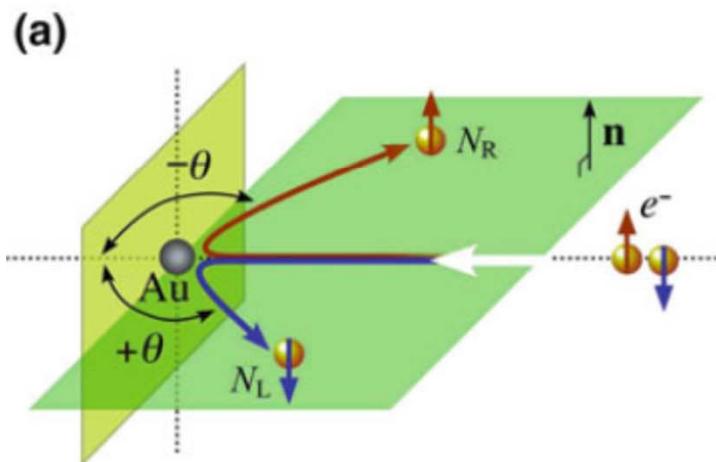
- Magnetic moment of electron:

$$\mu_e = -\frac{g_s e}{2mc} \mathbf{S}$$

- Interaction between electron and effective B field of nucleus:

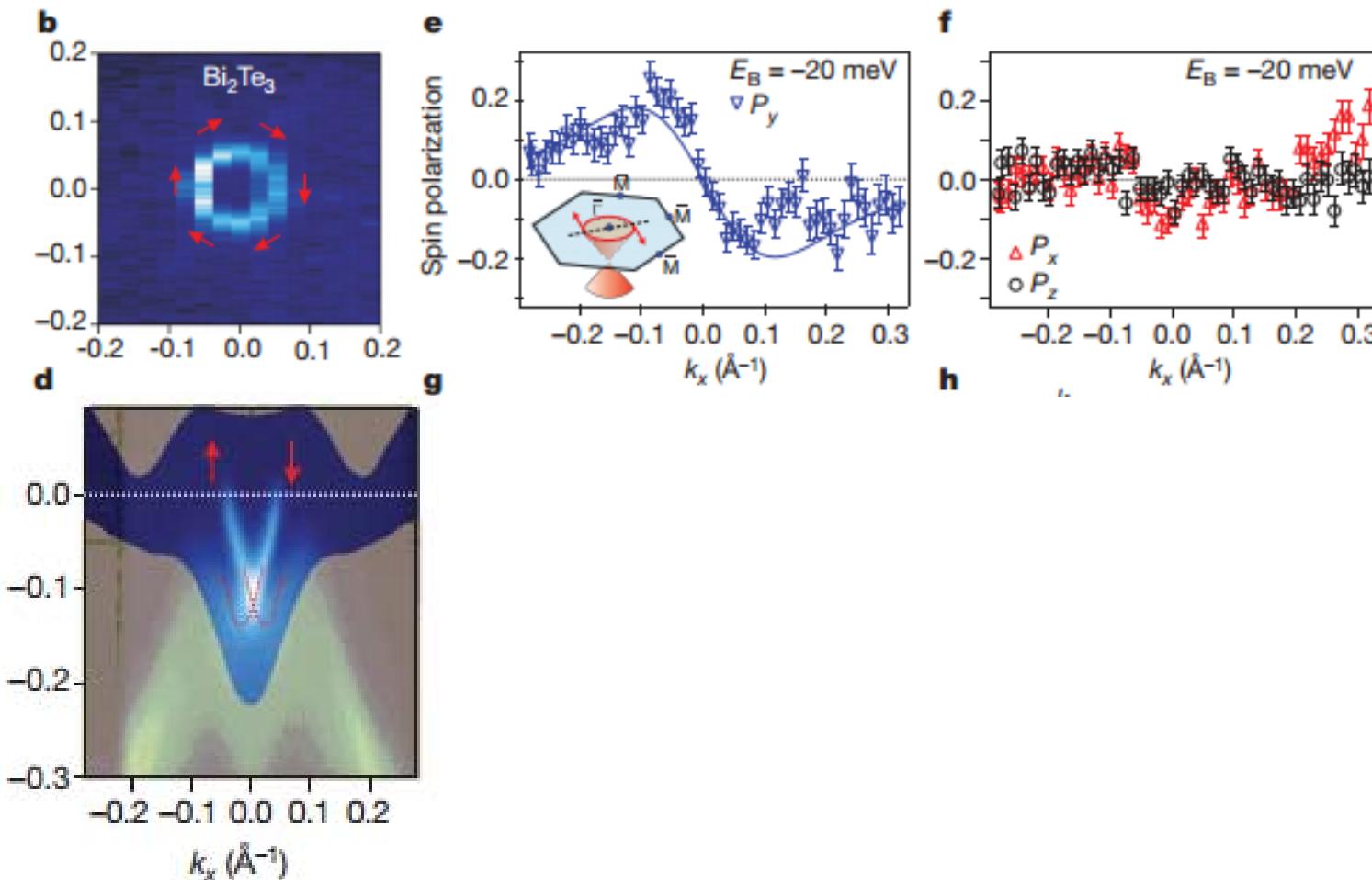
$$v_{LS} = -\mu_e \cdot \mathbf{B} = \frac{Ze^2}{2m^2 c^2 r^3} \mathbf{L} \cdot \mathbf{S}$$

- Scattering cross section has angular asymmetry



A. Takayama, *High-resolution spin-resolved photoemission spectrometer and the Rashba effect in Bismuth thin films* (2015)

Spin texture of Bi_2Te_3 via Mott scattering



Major contribution of 3D topological insulators: playground for time-resolved ARPES

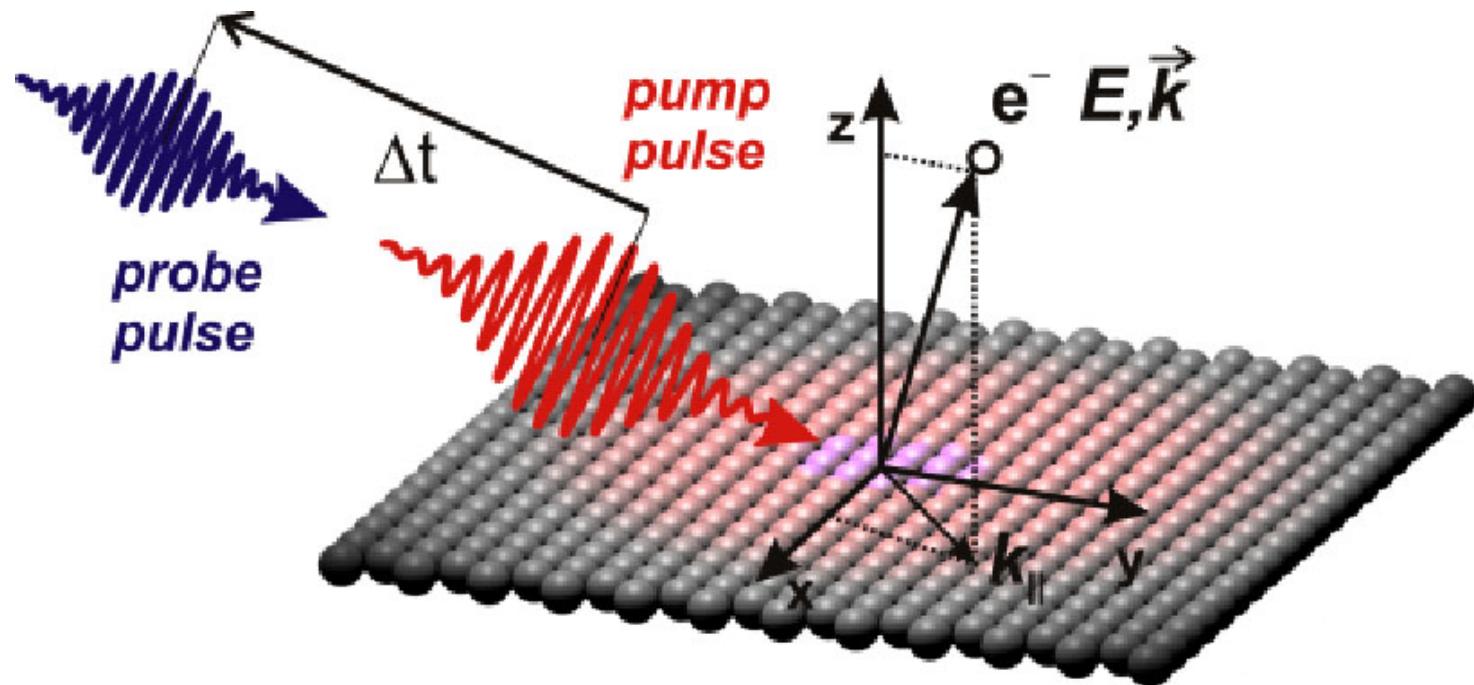
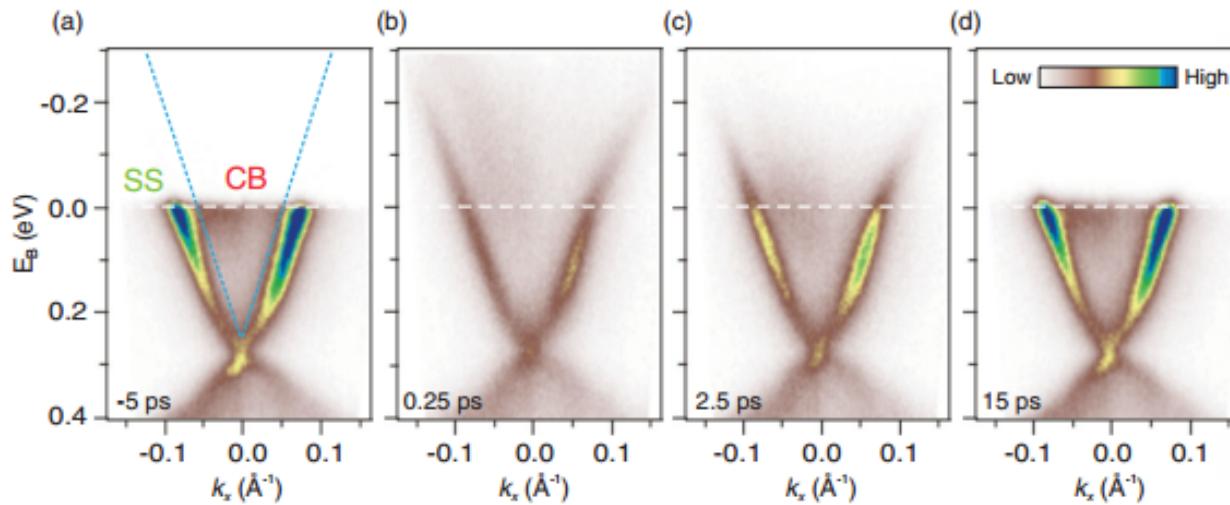
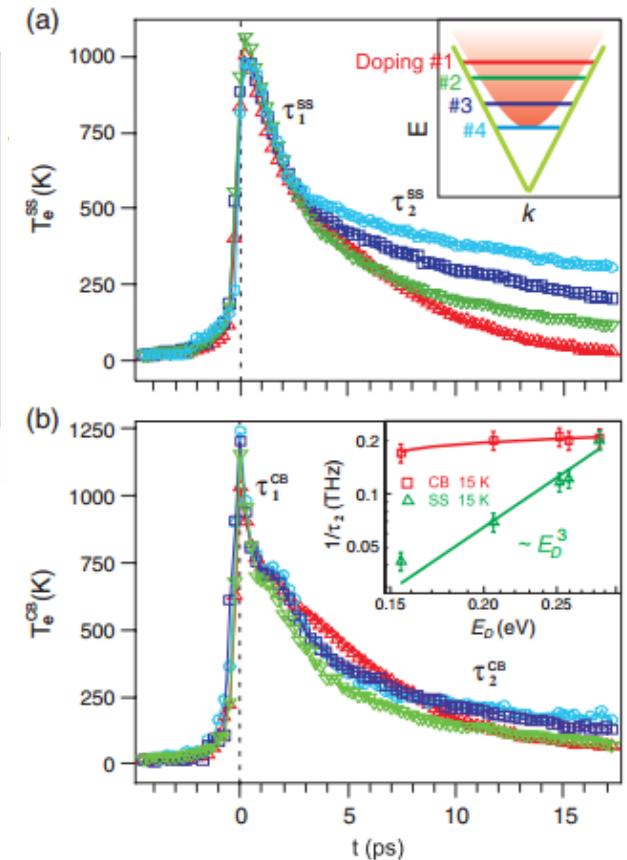


Image source: http://www.fhi-berlin.mpg.de/pc/PCres_methods.html

Surface-bulk coupling in Bi_2Se_3

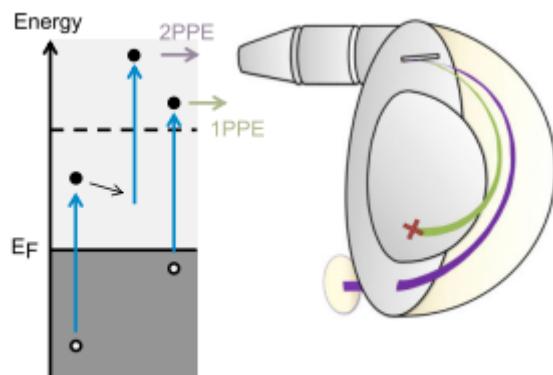


- 1.5 eV pump, 6 eV probe
- Pump deposits energy into **electrons**, effectively giving them higher temperature than surrounding lattice
- In ordinary metals: electron thermalization with lattice set by e-ph coupling
- In metallic surface state: hot electrons in surface state can cool down faster by thermalizing with bulk bands first



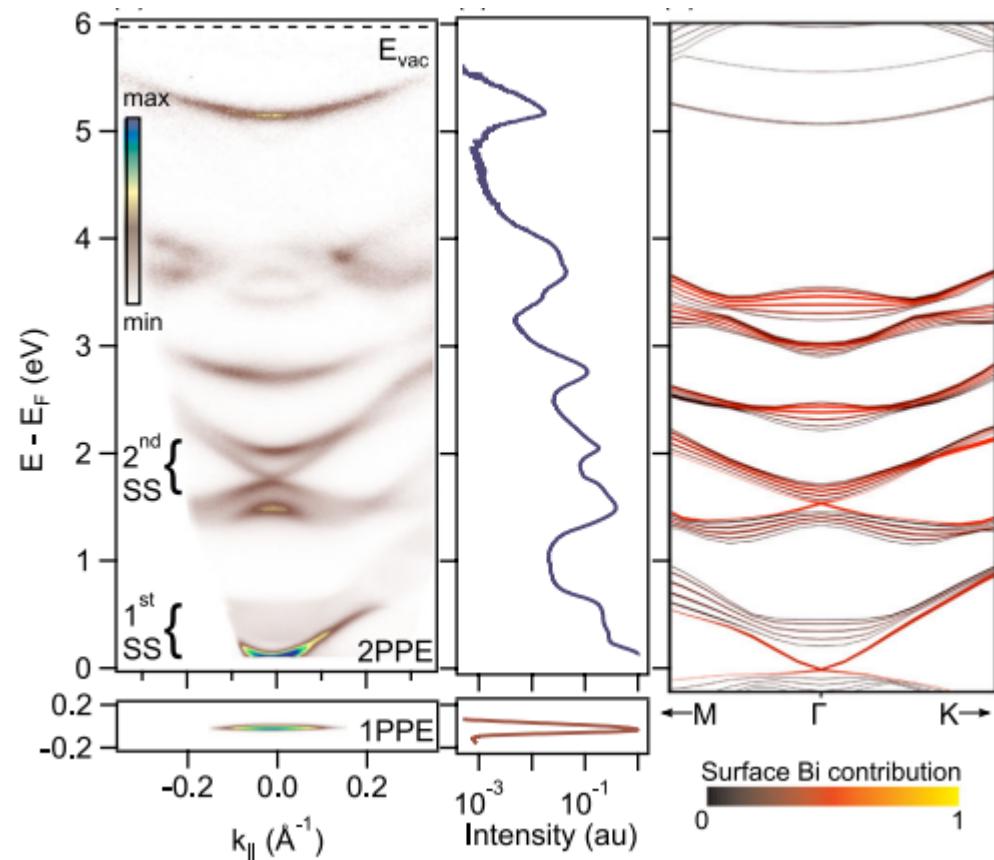
2 photon photoemission (2PPE) as a substitute for inverse photoemission

Photoemission	Photon in, electron out	Measure occupied electronic states	Sub-meV resolution common
Inverse photoemission	Electron in, photon out	Measure unoccupied electronic states	~500 meV resolution



- Use time-resolved ARPES to measure unoccupied states
- Pulse 1 (pump): make excitation into unoccupied state
 - Pulse 2 (probe): perform photoemission out of pump-populated unoccupied state
 - Time resolution is not very important, but light **intensity** is because this is 2nd order process

2 PPE experiments in Bi_2Se_3



- 1.5 eV pump, 5.98 eV probe, $\Delta t \sim 100 fs$
- 2nd surface state observed above E_F !
- Applicable to many different materials

Floquet-Bloch states

- Spatially periodic:

$$H(r + R) = H(r)$$

$$\Psi_{nk}(r) = e^{ik \cdot r} u_{nk}(r)$$

$$u_{nk}(r + R) = u_{nk}(r)$$

$$\begin{aligned} k \text{ and } k + nG \\ (G = 2\pi/R) \end{aligned}$$

- Temporally periodic

$$H(t + T) = H(t)$$

$$\Psi_\alpha(t) = e^{-\frac{i}{\hbar}\epsilon_\alpha(t-t_0)}\phi_\alpha(t)$$

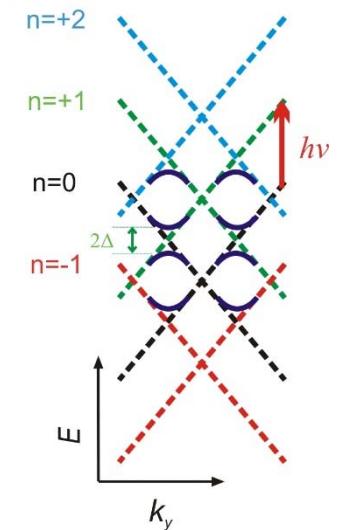
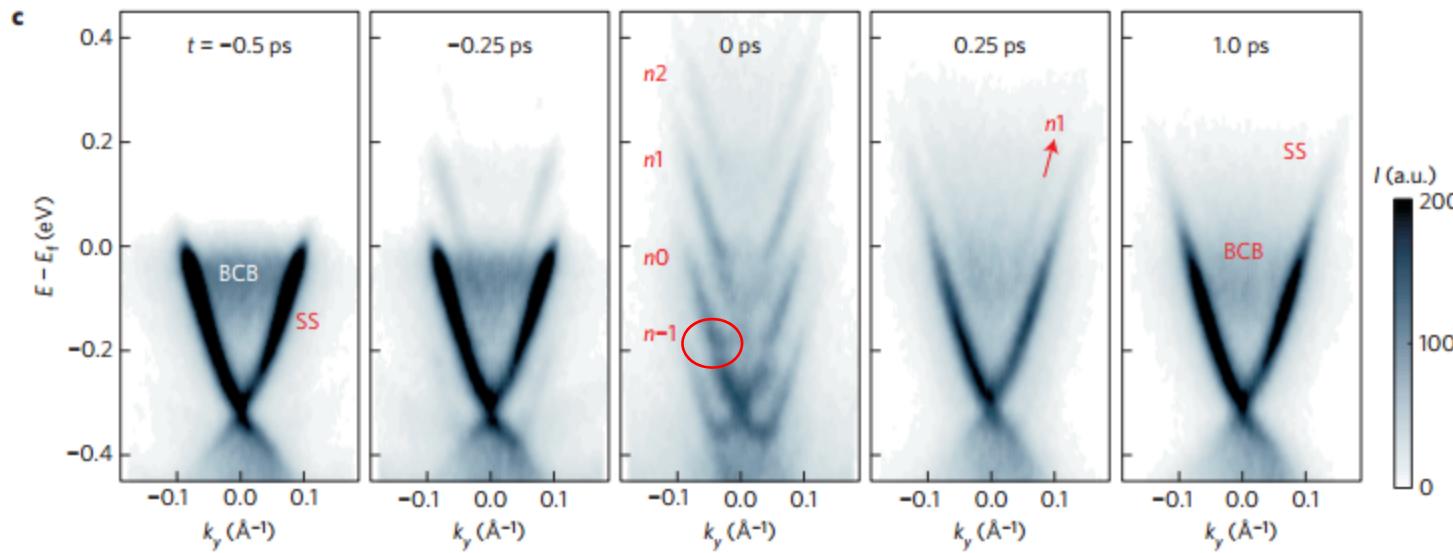
$$\phi_\alpha(t) = \phi_\alpha(t + T)$$

$$\begin{aligned} \epsilon_\alpha \text{ and } \epsilon_\alpha + n\hbar\omega \\ (\omega = 2\pi/T) \end{aligned}$$

If you have both spatially and temporally periodic Hamiltonian,
Eigenvalues are periodic both in k and $E!$ \rightarrow Floquet-Bloch states!

Creating new states of matter with light

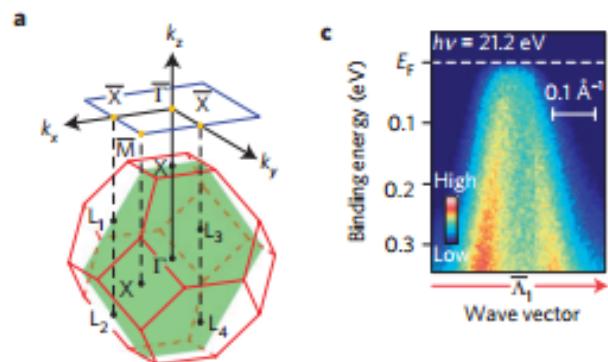
- Use mid-IR pump with energy **smaller** than band gap of Bi₂Se₃
- Use oscillating electric field of pump to create floquet-bloch state
- Photoinduced gaps at band crossings
- Circularly polarized light can open gap at Dirac point!



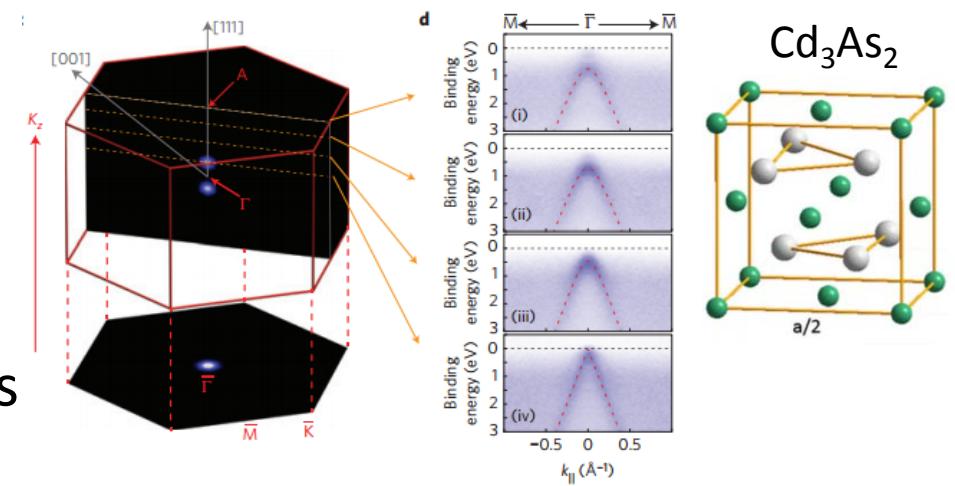
Wang *et al.* Science **342** 514 (2013)
Mahmood *et al.* Nat. Phys. **12** 453 (2016)

Intellectual descendants of topological insulators

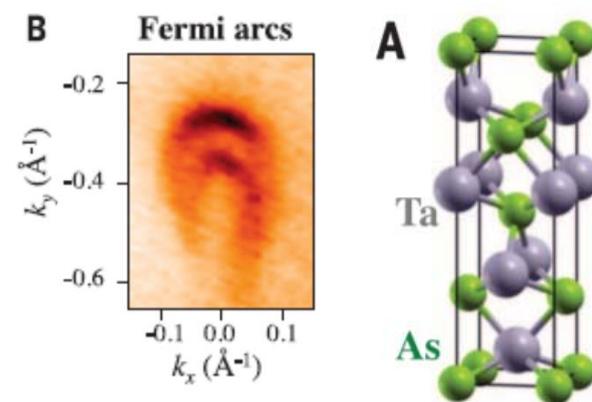
- Topological crystalline insulators (2012)
- Dirac Semimetals (2013)
- Weyl Semimetals (2015)
- Nodal line/chain/loop semimetals (2016)



TCI: Tanaka *et al.* Nat. Phys. **8** 800 (2012)



DSM: Liu *et al.*, Nat. Mater. **13** 677 (2014)

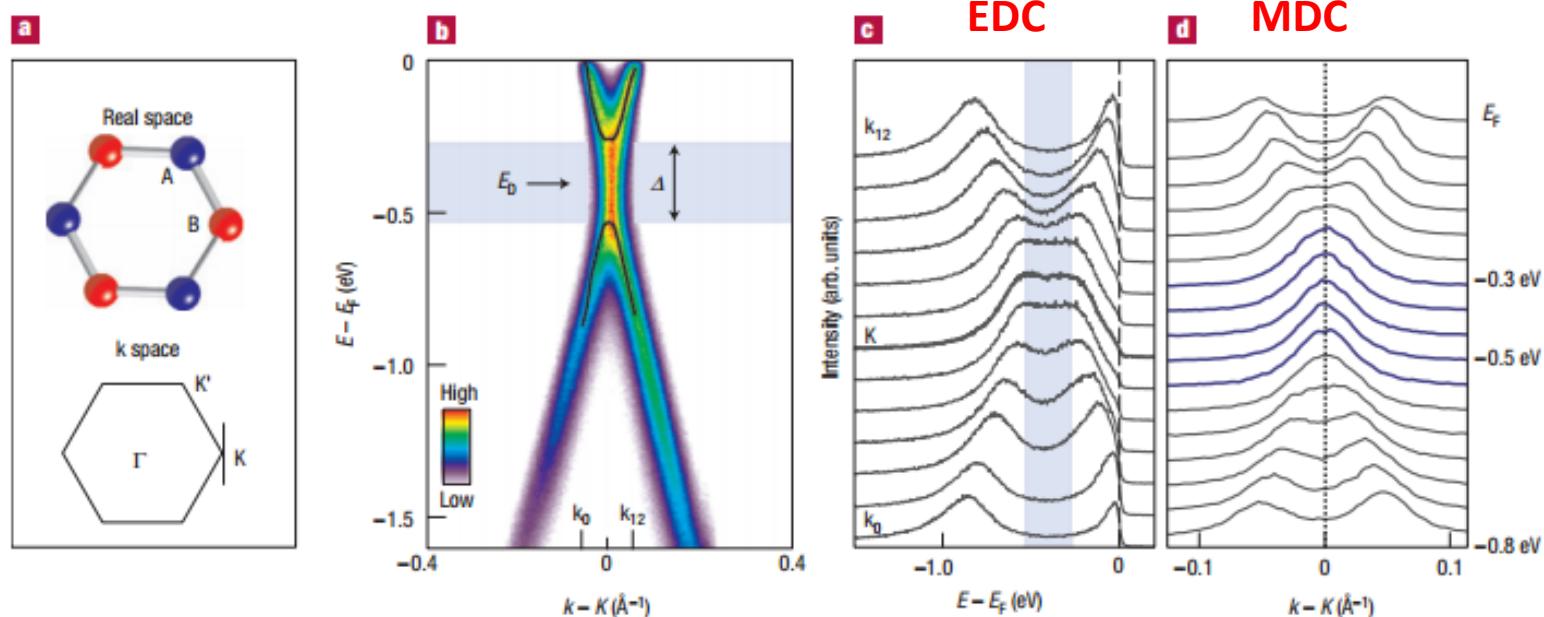


Xu *et al.* Science **349** 613 (2015)

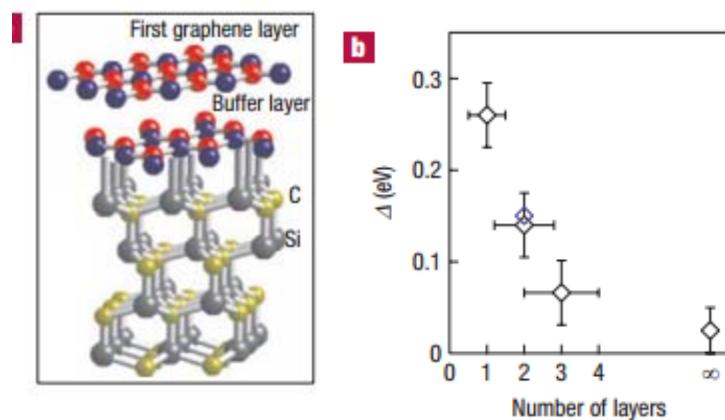
2D materials

A diverse platform for microARPES

ARPES on not-so-isolated graphene



Zhou *et al.* Nat. Mater. **6** 770 (2007)



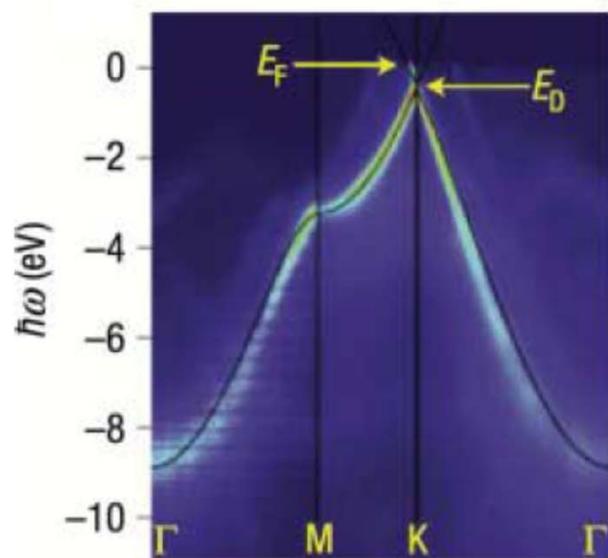
- Mass appears in dispersion because of sublattice symmetry breaking due to substrate

$$H_D = c\boldsymbol{\sigma} \cdot \boldsymbol{p} + mc^2\sigma_z$$

$$\boldsymbol{\sigma} = (\sigma_x, \sigma_y)$$
- Total of 36 ways to turn graphene massive (Ryu *et al*, PRB **80**, 205319 (2009))

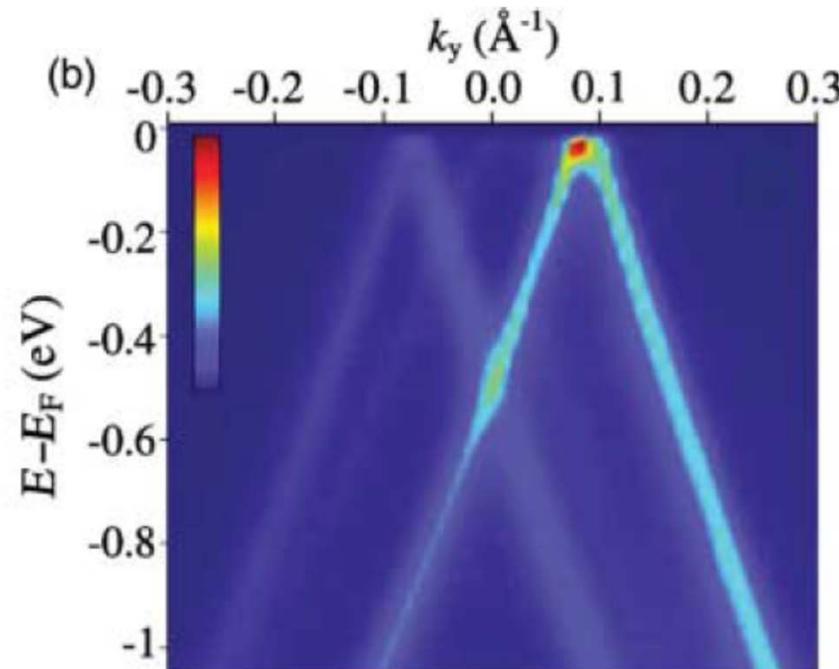
ARPES on isolated graphene

(a)

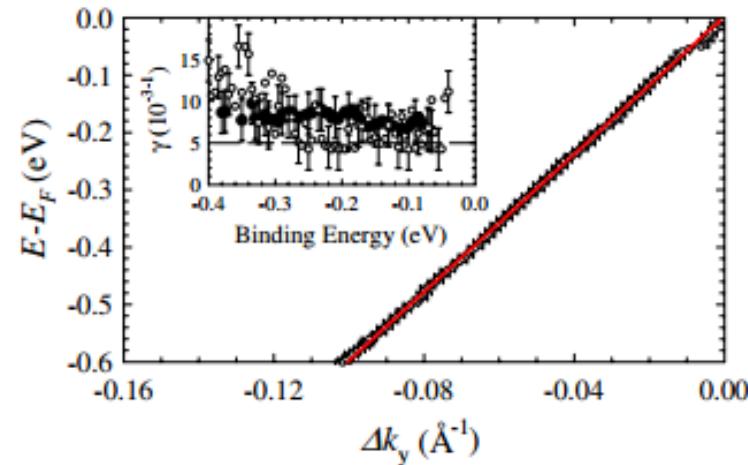


Bostwick *et al*, Nat. Phys.
3 36 (2007)

(b)

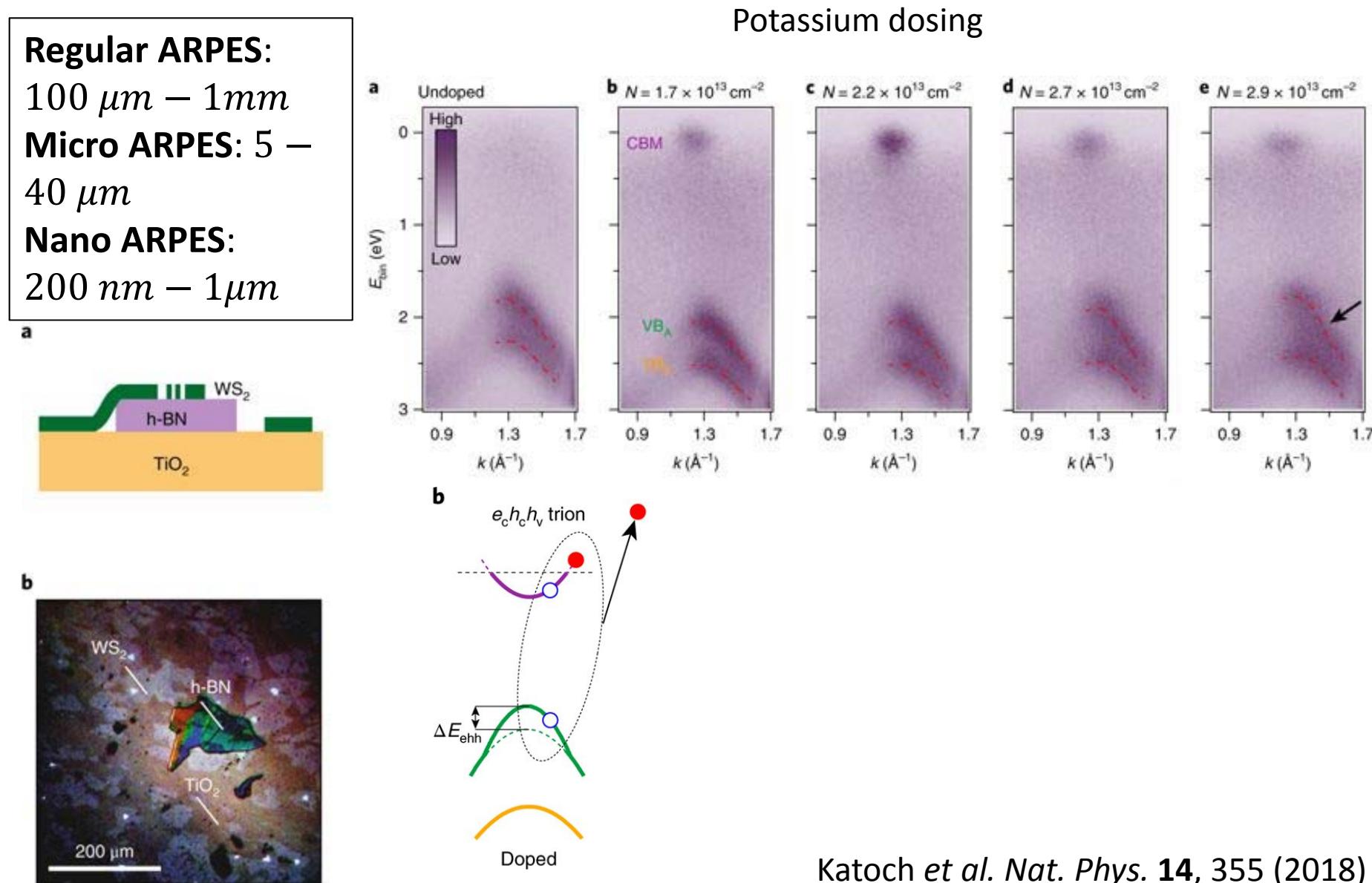


Sprinkle *et al*, PRL 103, 226803 (2009)



- Extra bands (right) from misoriented layers
- Band dispersion is linear over at least 600 meV

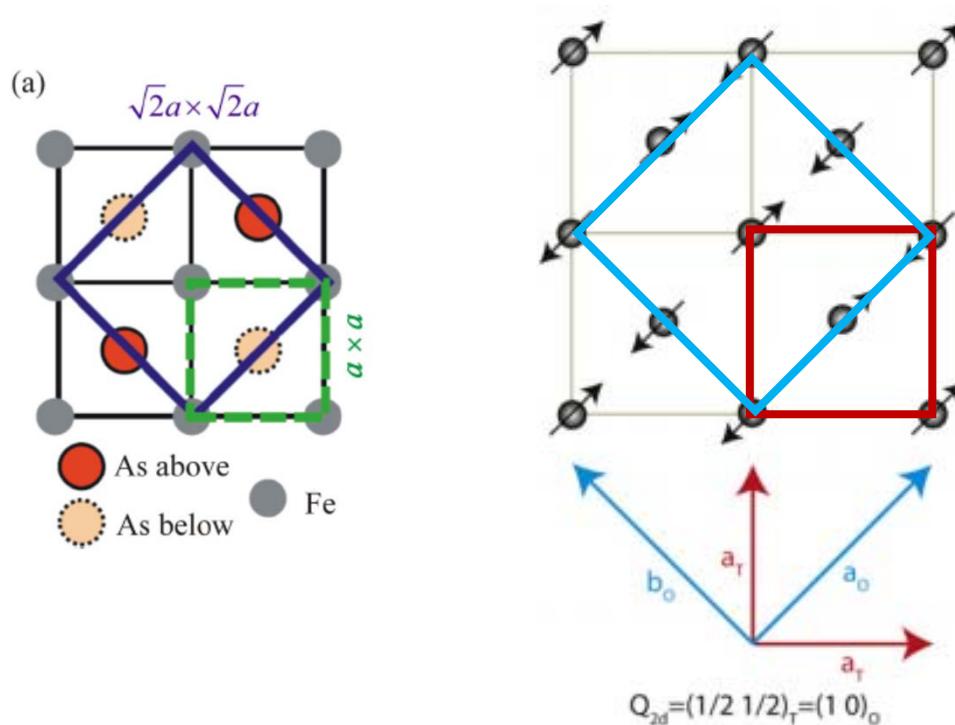
TDMC example: $\text{WS}_2/\text{h-BN}$ microARPES



Resources

- Lu, Vishik, *et al*, *Angle-resolved photoemission studies of quantum materials*, Ann. Rev. Cond. Matt. Phys., **3** 129 (2012)
- Hashimoto, Vishik, *et al*, *Energy gaps in high-transition-temperature cuprates superconductors*, Nat. Phys. **10** 483 (2014)
- Gedik and Vishik, *Photoemission of quantum materials*, Nat. Phys. **13** 1029 (2017)
- Contemporary Concepts of Condensed Matter Science, Volume 6, Pages 1-324 (2013) **Topological Insulators**, Chapters 1,2, 6
<http://www.sciencedirect.com/science/bookseries/15720934/6/supp/C>
- T.O. Wehling *et al*. “Dirac Materials” *Advances in Physics*, **63** p1-76 (2014)
<http://www.tandfonline.com/doi/abs/10.1080/00018732.2014.927109>
- Cattelan and Fox, *A Perspective on the Application of Spatially Resolved ARPES for 2D Materials*, Nanomaterials, **8**, 284 (2018)

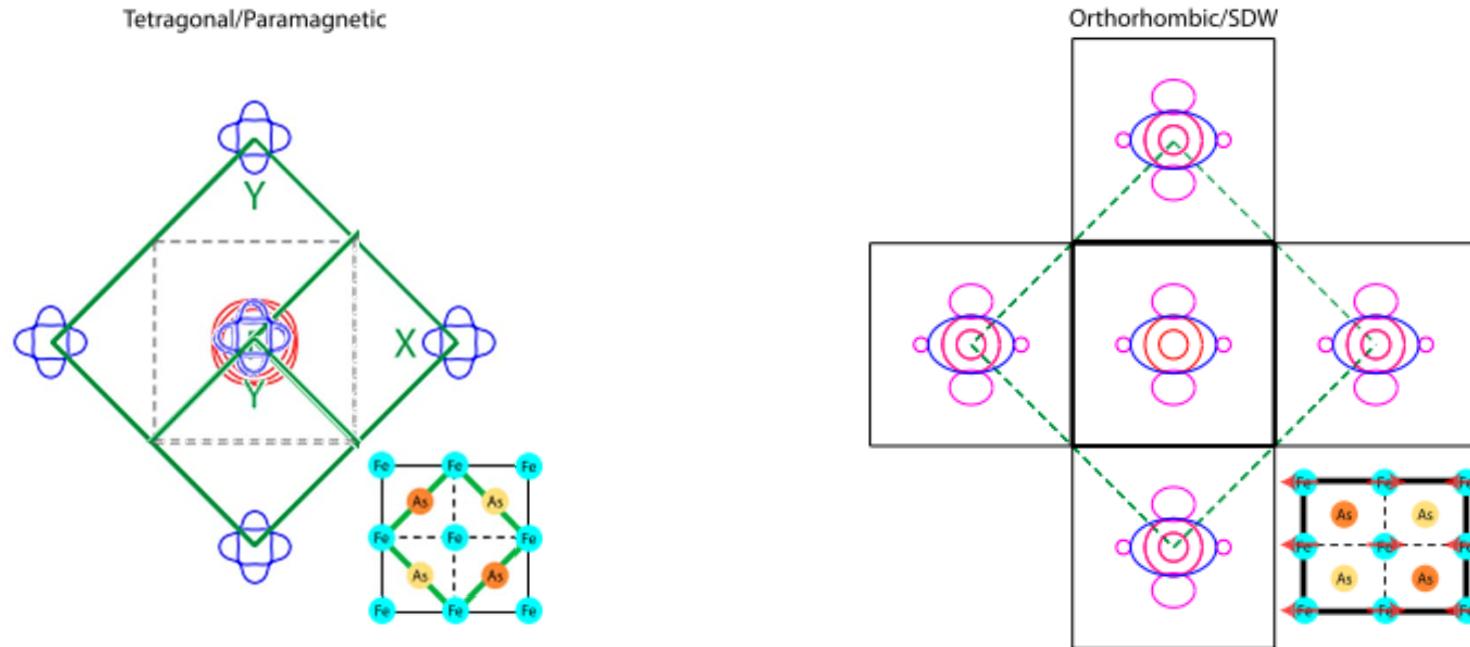
Magnetism and structural phase transition in 122 materials



*Structural and magnetic ordering have same unit cell, but orthorhombic phase transition usually happens first

Lumsden *et al*, J. Phys.: Condens. Matter **22** 203203 (2010)

Expected FS reconstruction



Note broken 4-fold rotation symmetry!

Problem: twinning

BaFe_2As_2

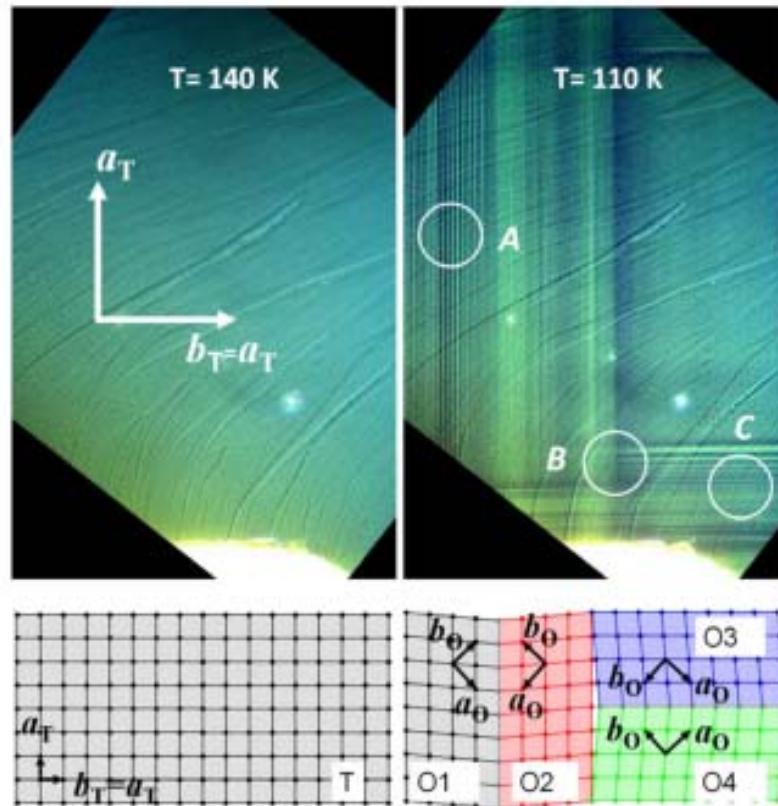
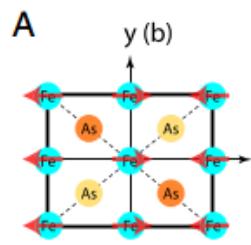
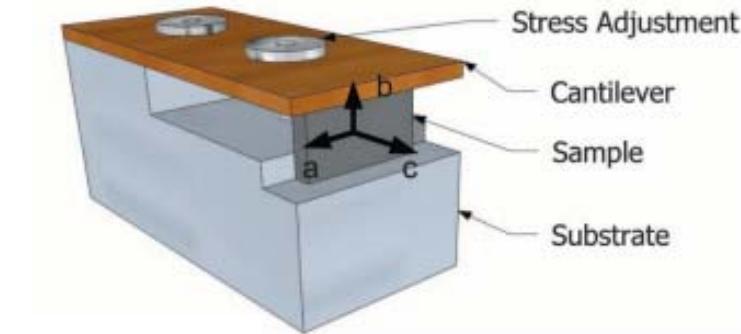


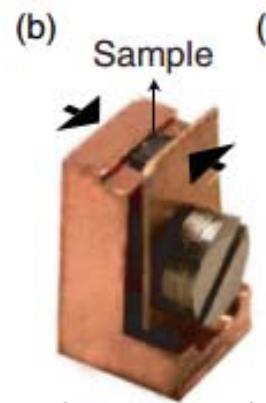
Image size is several hundred microns and characteristic domain size is 10-50 microns

Tanatar *et al.* PRB **79**, 180508R (2009)

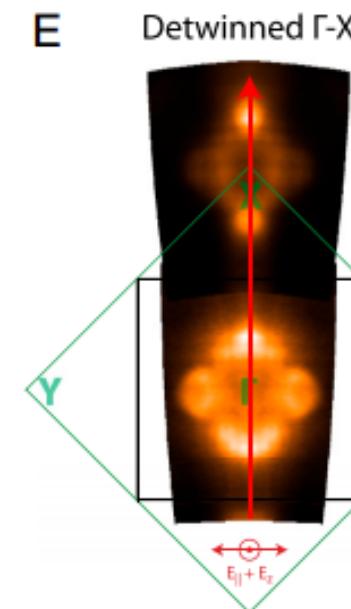
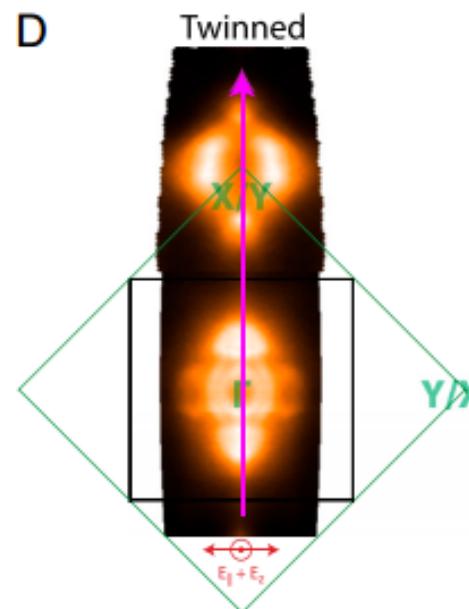
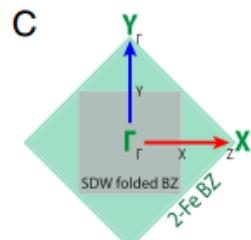
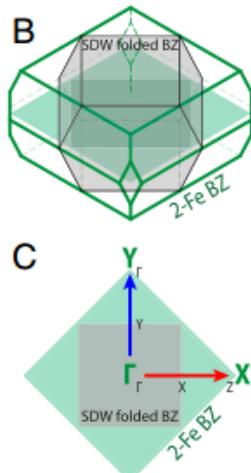
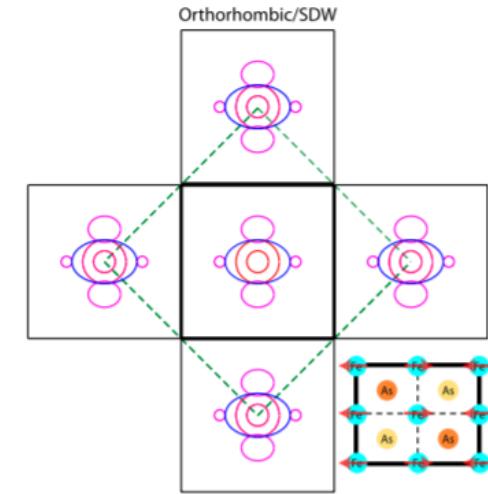
Mechanical de-twinning



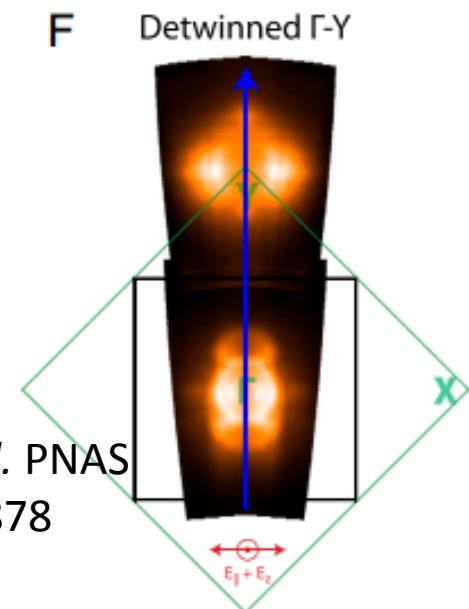
Chu *et al*, Science
329 p824 (2010)



Material: BaFe_2As_2

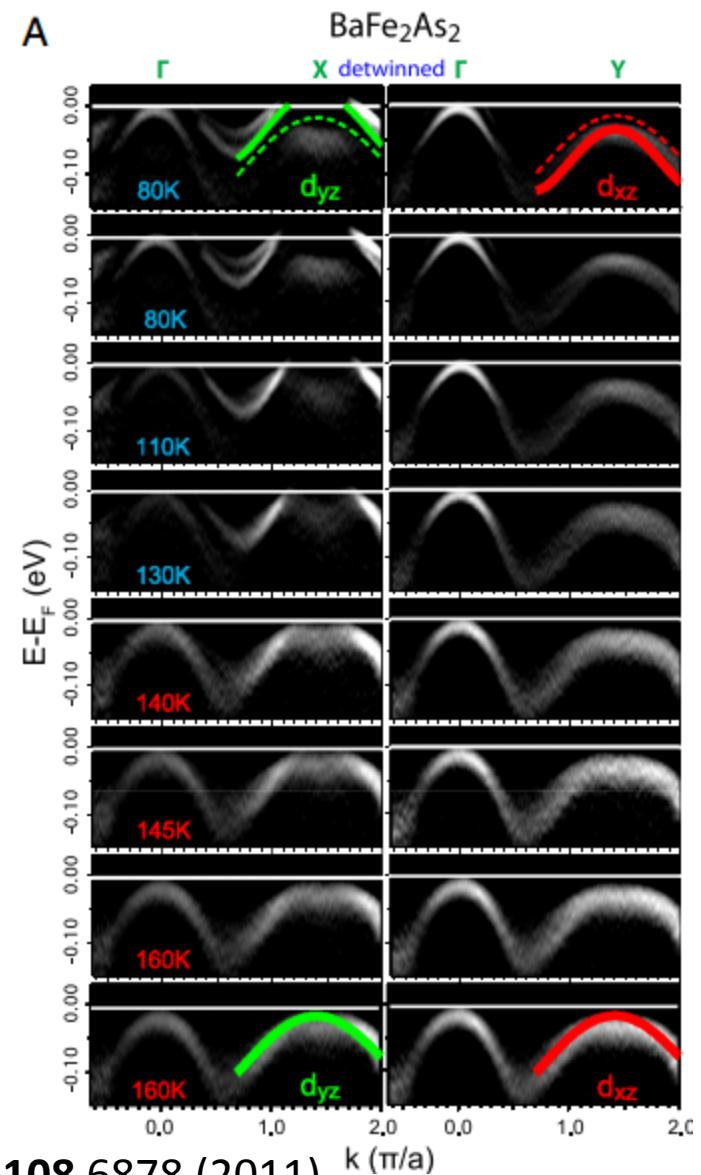
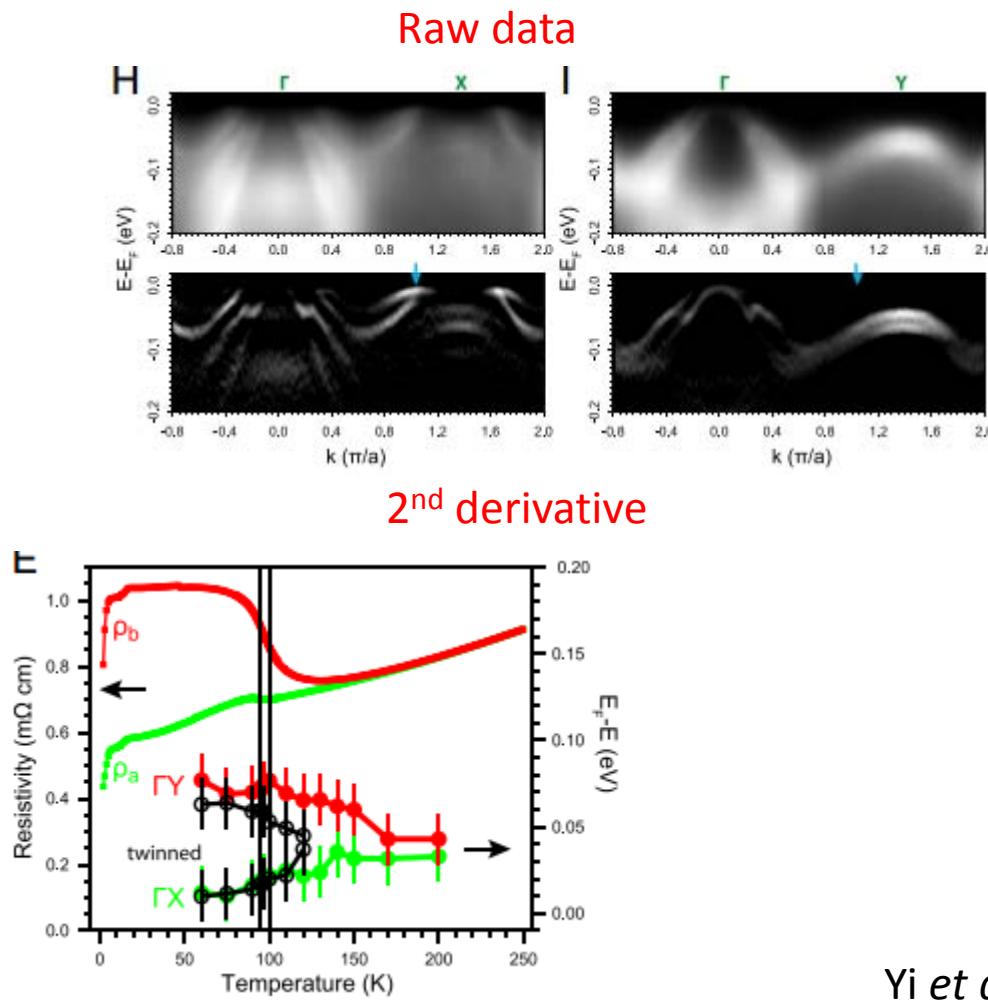


Yi *et al.* PNAS
108 6878
(2011)



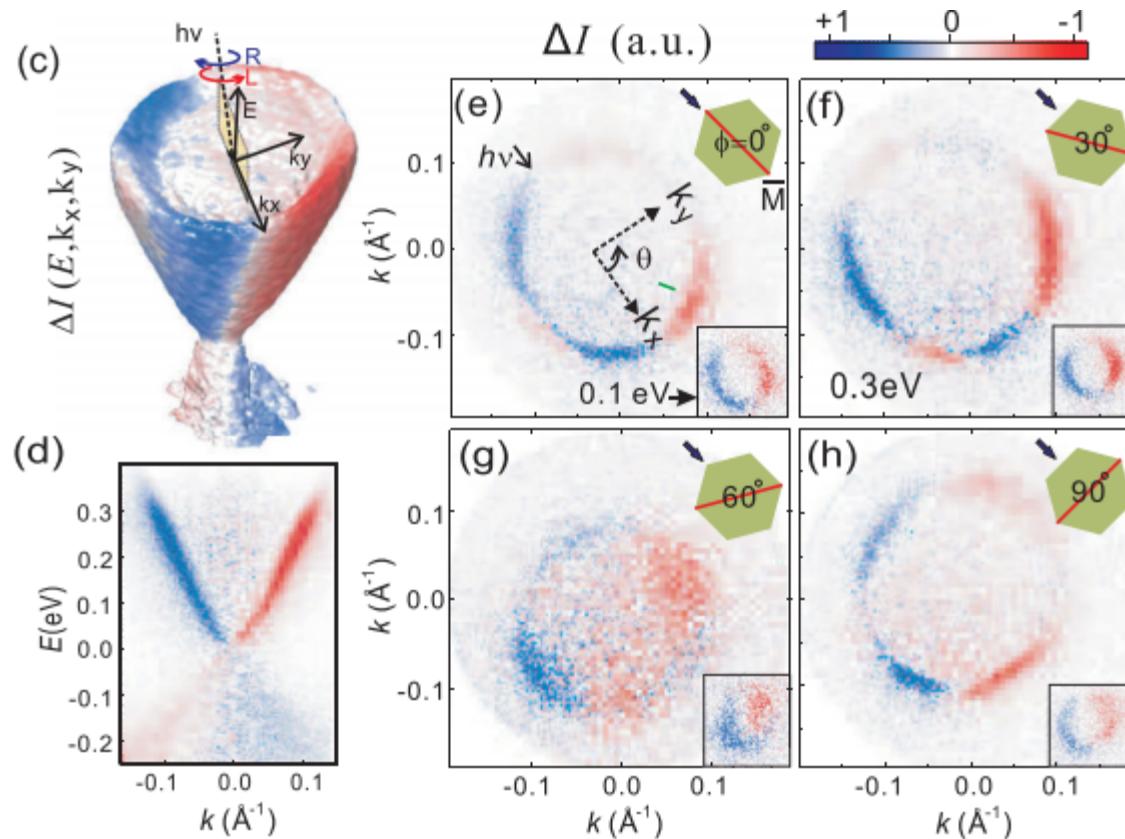
Signatures of band folding: extra bands

Material: BaFe_2As_2



Spin texture via circular dichroism

1. Measure ARPES spectrum with left-circularly polarized (LCP) light
2. Measure ARPES spectrum with right-circularly polarized (RCP) light
3. $\Delta I(E, k_x, k_y) = I_{LCP} - I_{RCP}$



Wang *et al.* PRL **107**,
207602 (2011)